



ISO5500 2.5A 隔离式 IGBT、MOSFET 栅极驱动器

1 特性

- 2.5A 最大峰值输出电流
- 将 IGBT 驱动至高达 $I_C=150A$, $V_{CE}=600V$
- 电容隔离式故障反馈
- CMOS/TTL 兼容输入
- 300ns 最大传播延迟
- 绝缘栅双极型晶体管 (IGBT) 软关断
- 集成故障安全 IGBT 保护
 - 高 $V_{CE}(\text{DESAT})$ 保护
 - 带滞后的欠压闭锁 (UVLO) 保护
- 用户可配置功能
 - 反向、非反向输入
 - 自动复位
 - 自动关断
- 宽 V_{CC1} 范围: 3V 至 5.5V
- 宽 V_{CC2} 范围: 15V 至 30V
- 运行温度: -40°C 至 125°C
- 宽体小外形尺寸 (SO)-16 封装
- $\pm 50\text{kV}/\mu\text{s}$ 瞬态抗扰度, 典型值
- 安全及管理批准:
 - 符合 DIN V VDE V 0884-10 (VDE V 0884-10) 和 DIN EN 61010-1 的 VDE 6000 V_{PK} 基础隔离
 - 符合 UL 1577 标准且长达 1 分钟的 $4,243 V_{RMS}$ 隔离
 - CSA 组件接受通知 #5A, IEC 61010-1 和 IEC 60950-1 终端设备标准

2 应用范围

- 隔离式 IGBT 和 MOSFET 驱动输入
 - 电机控制
 - 运动控制
 - 工业变频器
 - 开关模式电源

3 说明

ISO5500 是一款用于 IGBT 和 MOSFET 的隔离式栅极驱动器, 其具有高达 $I_C=150A$ 和 $V_{CE}=600V$ 的额定功率。输入 TTL 逻辑和输出功率级由一个电容、二氧化硅 (SiO_2), 绝缘格栅隔离开来。当与隔离式电源配合使用时, 这些器件可以阻止高电压、隔离接地, 并防止噪声电流进入本地接地和干扰或损坏敏感的电路。

在一个欠压闭锁电路 (UVLO) 监视输出电源的同时, 此器件为 IGBT 和 MOSFET 提供过流保护 (DESAT) 功能以保证足够的栅极驱动电压。如果输出电源电压下降至低于 12V, 通过将栅极驱动输出驱动至一个逻辑低电平状态, UVLO 将功率晶体管关闭。

对于一个 DESAT 故障, 在防止较大 di/dt 感应电压尖峰出现的同时, ISO5500 启动一个软关断过程来将 IGBT/MOSFET 电流缓慢减少至零。然后穿过隔离栅发送一个故障信号, 有效驱动开漏 $\overline{\text{FAULT}}$ 输出低电平并且禁用器件输入。输入在 $\overline{\text{FAULT}}$ 引脚为低电平的时间内被阻断。在输入针对一个输出低电平状态进行配置之前, $\overline{\text{FAULT}}$ 保持低电平, 随后是一个 $\overline{\text{RESET}}$ 引脚上的逻辑低电平输入。

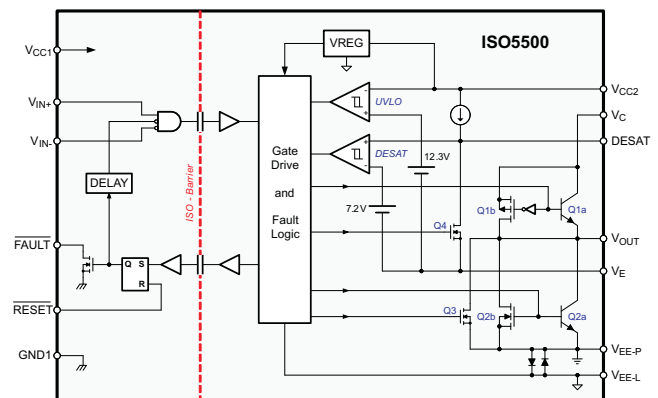
ISO5500 采用一个 16 引脚小外形尺寸集成电路 (SOIC) 封装, 额定运行温度范围为 -40°C 至 125°C 。

器件信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
ISO5500	SOIC (16)	10.30mm x 7.50mm

(1) 要了解所有可用封装, 请见数据表末尾的可订购产品附录。

功能方框图



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4 修订历史记录

Changes from Revision C (June 2013) to Revision D Page

• 已添加 引脚配置和功能部分, ESD 额定值表, 特性描述部分, 器件功能模式, 应用和实施部分, 电源相关建议部分, 布局部分, 器件和文档支持部分以及机械、封装和可订购信息部分	1
• VDE 标准更改为 DIN V VDE V 0884-10 (VDE V 0884-10):2006-12	1
• Added FAULT limits to Absolute Maximum Ratings	4

Changes from Revision B (May 2013) to Revision C Page

• 已更改 V_{CE} 从 1200V 至 600V	1
• Added the Thermal Information table inside the data sheet below the Absolute Maximum Ratings table	5
• Changed row V_{IORM} and V_{PR} specification from V_{IORM} of 1200V _{pk} to 680 V _{pk}	17
• Changed 1200 V _{pk} in the Regulatory Information table from 1200 V _{pk} to 680 V _{pk}	17
• Deleted last row of the IEC 60664-1 Rating Table	18
• Added Isolation Lifetime at a Maximum Continuous Working Voltage table	18
• Added Function Table under the Functional Block Diagram	25

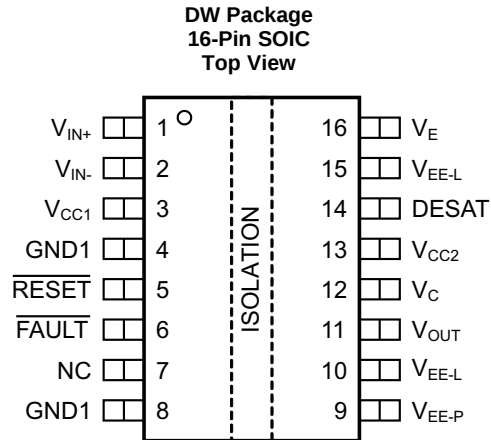
Changes from Revision A (July 2012) to Revision B Page

• 更改了监管部门批准列表	1
• Changed the REGULATORY INFORMATION table, VDE Column From: File Number: pending To: File Number: 40016131	17
• Changed the REGULATORY INFORMATION table, CSA Column From: File Number: pending To: File Number: 220991	17

Changes from Original (September 2011) to Revision A Page

• 将器件状态从: 产品预览更改为: 量产数据	1
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5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	V_{IN+}	I	Noninverting gate drive voltage control input
2	V_{IN-}	I	Inverting gate drive voltage control input
3	V_{CC1}	Supply	Positive input supply (3 V to 5.5 V)
4,8	GND1	Ground	Input ground
5	$\overline{RESET}$	I	$\overline{FAULT}$ reset input
6	$\overline{FAULT}$	O	Open-drain output. Connect to 3.3k pullup resistor
7	NC	NC	Not connected
9	V_{EE-P}	Supply	Most negative output-supply potential of the power output. Connect externally to pin 10.
10, 15	V_{EE-L}	Supply	Most negative output-supply potential of the logic circuitry. Pin 10 and 15 are internally connected. Connect at least pin 10 externally to pin 9. Pin 15 can be floating.
11	V_{OUT}	O	Gate drive output voltage
12	V_C	Supply	Gate driver supply. Connect to V_{CC2} .
13	V_{CC2}	Supply	Most positive output supply potential
14	DESAT	I	Desaturation voltage input
16	V_E	Ground	Gate drive common. Connect to IGBT Emitter.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Supply voltage, V_{CC1}		-0.5	6	V
Total output supply voltage, $V_{OUT(total)}$	$(V_{CC2} - V_{EE-P})$	-0.5	35	V
Positive output supply voltage, V_{OUT+}	$(V_{CC2} - V_E)$	-0.5	35 – $(V_E - V_{EE-P})$	V
Negative output supply voltage, V_{OUT-}	$(V_E - V_{EE-P})$	-0.5	V_{CC2}	V
Voltage at	DESAT	$V_E - 0.5$	V_{CC2}	V
	V_{IN+} , V_{IN-} , $\overline{RESET}$, $\overline{FAULT}$	-0.5	6	
Peak gate drive output voltage	$V_{O(peak)}$	-0.5	V_{CC2}	V
Collector voltage, V_C		-0.5	V_{CC2}	V
Output current, I_O ⁽¹⁾			±2.8	A
$\overline{FAULT}$ output current, I_{FL}			±20	mA
Maximum junction temperature, T_J			170	°C
Storage temperature, T_{stg}		-65	150	°C

(1) Maximum pulse width = 10 μ s, maximum duty cycle = 0.2%.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	
	Machine model JEDEC JESD22-A115-A	±200	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC1}	Supply voltage	3		5.5	V
$V_{OUT(total)}$	Total output supply voltage ($V_{CC2} - V_{EE-P}$)	15		30	V
V_{OUT+}	Positive output supply voltage ($V_{CC2} - V_E$)	15		30 – $(V_E - V_{EE-P})$	V
V_{OUT-}	Negative output supply voltage ($V_E - V_{EE-P}$)	0		15	V
V_C	Collector voltage	$V_{EE-P} + 8$		V_{CC2}	V
t_{ui}	Input pulse width	0.1			μ s
t_{uiR}	$\overline{RESET}$ Input pulse width	0.1			μ s
V_{IH}	High-level input voltage (V_{IN+} , V_{IN-} , $\overline{RESET}$)	2		V_{CC}	V
V_{IL}	Low-level input voltage (V_{IN+} , V_{IN-} , $\overline{RESET}$)	0		0.8	V
f_{INP}	Input frequency			520 ⁽¹⁾	kHz
V_{SUP_SR}	Supply Slew Rate (V_{CC1} or $V_{CC2} - V_{EE-P}$) ⁽²⁾			75	V/ms
T_J	Junction temperature	-40		150	°C
T_A	Ambient temperature	-40	25	125	°C

(1) If $T_A = 125^\circ\text{C}$, $V_{CC1} = 5.5\text{ V}$, $V_{CC2} = 30\text{ V}$, $R_G = 10\ \Omega$, $C_L = 1\text{ nF}$

(2) If V_{CC1} skew is faster than 75 V/ms (especially for the falling edge) then V_{CC2} must be powered up after V_{CC1} and powered down before V_{CC1} to avoid output glitches.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		ISO5500	UNIT
		DW (SOIC) 16 PINS	
θ_{JA}	Junction-to-ambient thermal resistance	76	°C/W
θ_{JCTop}	Junction-to-case (top) thermal resistance	34	
θ_{JB}	Junction-to-board thermal resistance	36	
Ψ_{JT}	Junction-to-top characterization parameter	8	
Ψ_{JB}	Junction-to-board characterization parameter	35	
T_{SHDN+}	Thermal Shutdown	185	°C
T_{SHDN-}		173	°C
$T_{SHDN-HYS}$	Thermal Shutdown Hysteresis	12	°C
P_D	Power Dissipation See Equation 2 through Equation 6	592	mW

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, [SPRA953](#).

6.5 Electrical Characteristics

All typical values are at $T_A = 25^\circ\text{C}$, $V_{CC1} = 5\text{ V}$, $V_{CC2} - V_E = 30\text{ V}$, $V_E - V_{EE-P} = 0\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{CC1}	Supply current	Quiescent	V _I = V _{CC1} or 0 V, No load, See Figure 1 , Figure 2 , Figure 28 , and Figure 29	5.5	8.5	mA
		300 kHz		5.7	8.7	
I _{CC2}	Supply current	Quiescent	V _I = V _{CC1} or 0 V, No load, See Figure 3 through Figure 5 , Figure 30 , and Figure 31	8.4	12	mA
		300 kHz		9	14	
I _{CH}	High-level collector current	I _{OUT} = 0, See Figure 27 and Figure 30			1.3	mA
		I _{OUT} = −650 μA, See Figure 27 and Figure 30			1.9	
I _{CL}	Low-level collector current	See Figure 27 and Figure 31			0.4	mA
I _{EH}	V _E High-level supply current	See Figure 6 and Figure 40	−0.5	−0.3		mA
I _{EL}	V _E Low-level supply current	See Figure 6 and Figure 41	−0.8	−0.53		mA
I _{IH}	High-level input leakage	I _N from 0 to V _{CC}			10	μA
I _{IL}	Low-level input leakage		−10			
I _{FH}	High-level $\overline{\text{FAULT}}$ pin output current	V _{FAULT} = V _{CC1} , no pull-up, See Figure 33	−10		10	μA
I _{FL}	Low-level $\overline{\text{FAULT}}$ pin output current	V _{FAULT} = 0.4 V, no pull-up, See Figure 34	5	12		mA
V _{IT+(UVLO)}	Positive-going UVLO threshold voltage	See Figure 32	11.6	12.3	13.5	V
V _{IT−(UVLO)}	Negative-going UVLO threshold voltage			11.1	12.4	
V _{HYS (UVLO)}	UVLO Hysteresis voltage (V _{IT+} − V _{IT−})			0.7	1.2	
I _{OH}	High-level output current	V _{OUT} = V _{CC2} − 4 V ⁽¹⁾ , See Figure 7 and Figure 35	−1	−1.6		A
		V _{OUT} = V _{CC2} − 15 V ⁽²⁾ , See Figure 7 and Figure 35	−2.5			
I _{OL}	Low-level output current	V _{OUT} = V _{EE-P} + 2.5 V ⁽¹⁾ , See Figure 8 and Figure 36	1	1.8		A
		V _{OUT} = V _{EE-P} + 15 V ⁽²⁾ , See Figure 8 and Figure 36	2.5			
I _{OF}	Output-low fault current	V _{OUT} − V _{EE-P} = 14 V, See Figure 9 and Figure 37	90	140	230	mA
V _{OH}	High-level output voltage	I _{OUT} = −100 mA, See Figure 10 , Figure 11 and Figure 38	V _C −1.5	V _C −0.8		V
		I _{OUT} = −650 μA, See Figure 10 , Figure 11 and Figure 38	V _C −0.15	V _C −0.05		
V _{OL}	Low-level output voltage	I _{OUT} = 100 mA, See Figure 12 , Figure 13 and Figure 39		0.2	0.5	V
I _{CHG}	Blanking capacitor charging current	V _{DESAT} = 0 V to 6 V, See Figure 14 and Figure 42	−180	−270	−380	μA
I _{DSCHG}	Blanking capacitor discharge current	V _{DESAT} = 8 V, See Figure 42	20	45		mA

(1) Maximum pulse width is 50 μs , maximum duty cycle is 0.5%

(2) Maximum pulse width is 10 μs , maximum duty cycle is 0.2%

Electrical Characteristics (continued)

All typical values are at $T_A = 25^\circ\text{C}$, $V_{CC1} = 5\text{ V}$, $V_{CC2} - V_E = 30\text{ V}$, $V_E - V_{EE-P} = 0\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{DSTH} DESAT threshold voltage	$(V_{CC2} - V_E) > V_{TH-(UVLO)}$, See Figure 15 and Figure 42	6.7	7.2	7.7	V
CMTI Common mode transient immunity	$V_I = V_{CC1}$ or 0 V , V_{CM} at 1500 V , See Figure 43 through Figure 46	25	50		kV/ μS

6.6 Switching Characteristics

All typical values are at $T_A = 25^\circ\text{C}$, $V_{CC1} = 5\text{ V}$, $V_{CC2} - V_E = 30\text{ V}$, $V_E - V_{EE-P} = 0\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL} Propagation Delay	$R_G = 10\ \Omega$, $C_G = 10\text{ nF}$, 50 % duty cycle, 10 kHz input, $V_{CC2} - V_{EE} = 30\text{ V}$, $V_E - V_{EE-P} = 0\text{ V}$, See Figure 16 through Figure 19, Figure 26, Figure 47, Figure 49, and Figure 50	150	200	300	ns
t_{sk-p} Pulse Skew $ t_{PHL} - t_{PLH} $			1.7	10	ns
t_{sk-pp} Part-to-part skew ⁽¹⁾				45	ns
t_{sk2-pp} Part-to-part skew ⁽²⁾		-50		50	ns
t_r Output signal rise time			55		ns
t_f Output signal fall time	$R_G = 10\ \Omega$, $C_G = 10\text{ nF}$, $V_{CC2} - V_{EE-P} = 30\text{ V}$, $V_E - V_{EE-P} = 0\text{ V}$, See Figure 20 through Figure 25, Figure 48 and Figure 51		10		ns
$t_{DESAT(90\%)}$ DESAT sense to 90% VOUT delay			300	550	ns
$t_{DESAT(10\%)}$ DESAT sense to 10% VOUT delay			1.8	2.3	μs
$t_{DESAT(FAULT)}$ DESAT sense to $\overline{FAULT}$ low output delay			290	550	ns
$t_{DESAT(LOW)}$ DESAT sense to DESAT low propagation delay			180		ns
$t_{RESET(FAULT)}$ $\overline{RESET}$ to high-level $\overline{FAULT}$ signal delay		3	8.2	13	μs
$t_{UVLO(ON)}$ UVLO to VOUT high delay	1ms ramp from 0 V to 30 V		4		μs
$t_{UVLO(OFF)}$ UVLO to VOUT low delay	1ms ramp from 30 V to 0 V		6		μs
t_{FS} Failsafe output delay time from input power loss			2.8		μs

- (1) t_{sk-pp} is the maximum difference in same edge propagation delay times (either V_{IN+} to V_{OUT} or V_{IN-} to V_{OUT}) between two devices operating at the same supply voltage, same temperature, and having identical packages and test circuits.

$$\text{i.e. max} \left\{ \begin{aligned} & \left[t_{PHL-\max}(V_{CC1}, V_{CC2}, T_A) - t_{PHL-\min}(V_{CC1}, V_{CC2}, T_A) \right], \\ & \left[t_{PLH-\max}(V_{CC1}, V_{CC2}, T_A) - t_{PLH-\min}(V_{CC1}, V_{CC2}, T_A) \right] \end{aligned} \right\}$$

- (2) t_{sk2-pp} is the propagation delay difference in high-to-low to low-to-high transition (any of the combinations V_{IN+} to V_{OUT} or V_{IN-} to V_{OUT}) between two devices operating at the same supply voltage, same temperature, and having identical packages and test circuits.

$$\text{i.e.} \quad \begin{aligned} \min &= t_{PHL-\min}(V_{CC1}, V_{CC2}, T_A) - t_{PLH-\max}(V_{CC1}, V_{CC2}, T_A) \\ \max &= t_{PHL-\max}(V_{CC1}, V_{CC2}, T_A) - t_{PLH-\min}(V_{CC1}, V_{CC2}, T_A) \end{aligned}$$

6.7 Typical Characteristics

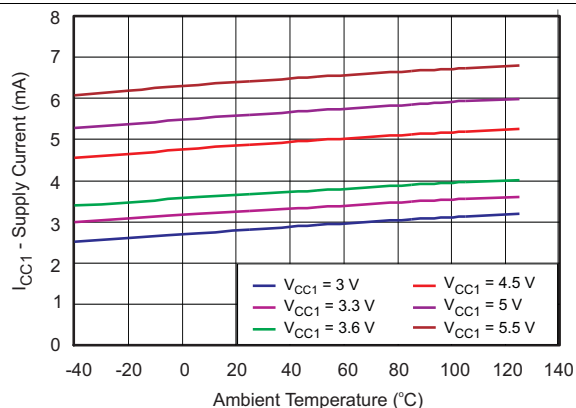


Figure 1. V_{CC1} Supply Current vs. Temperature

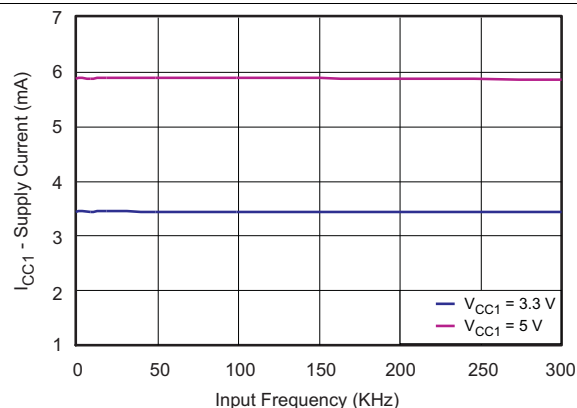


Figure 2. V_{CC1} Supply Current vs. Frequency

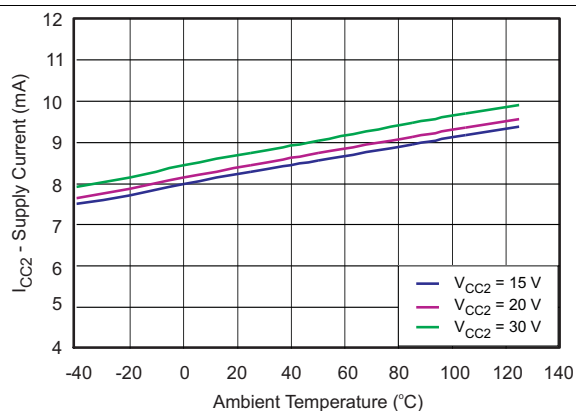


Figure 3. V_{CC2} Supply Current vs. Temperature

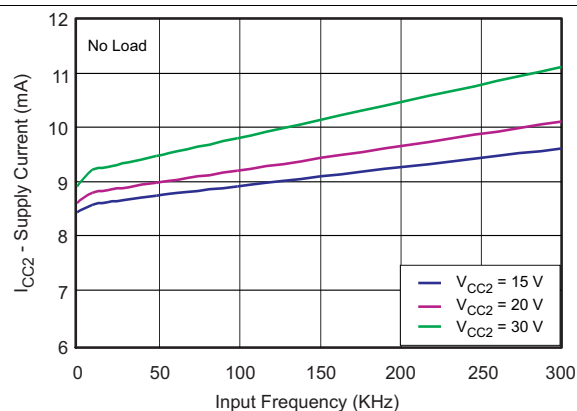


Figure 4. V_{CC2} Supply Current vs. Frequency

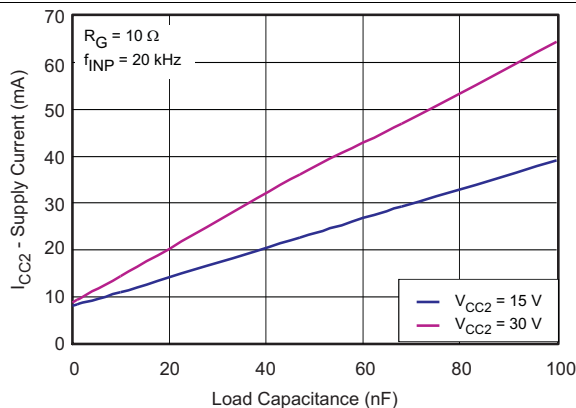


Figure 5. V_{CC2} Supply Current vs. Load Capacitance

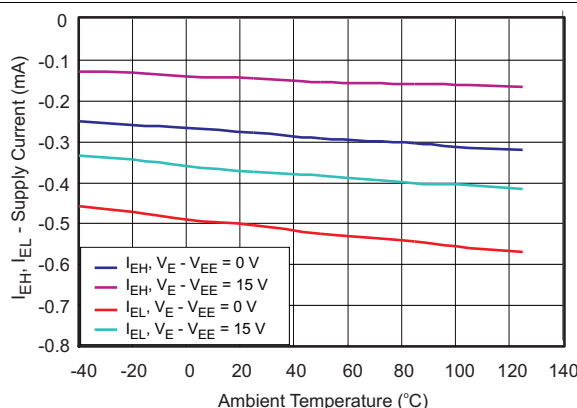


Figure 6. V_E Supply Current vs. Temperature

Typical Characteristics (continued)

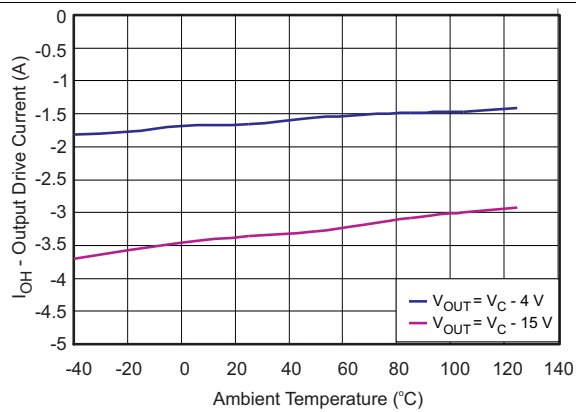


Figure 7. Output Drive Current vs. Temperature

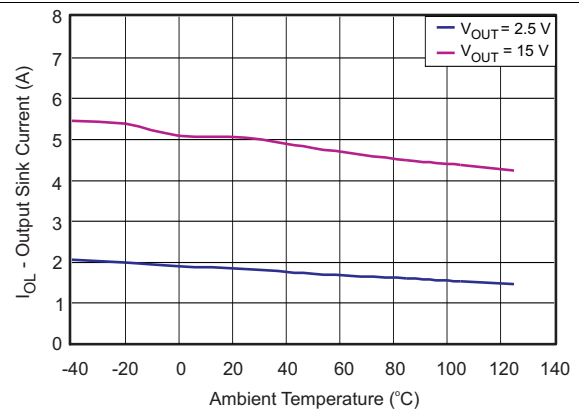


Figure 8. Output Sink Current vs. Temperature

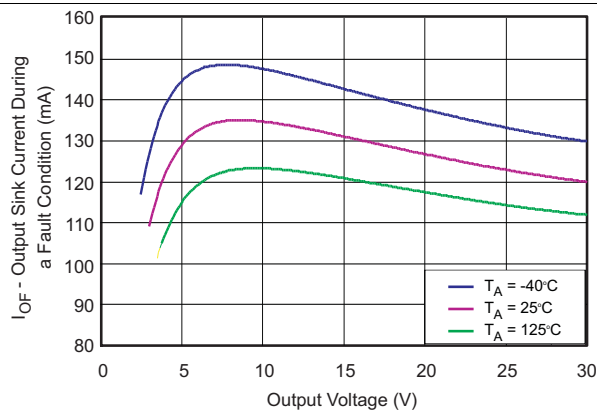


Figure 9. Output Sink Current During a Fault Condition vs. Output Voltage

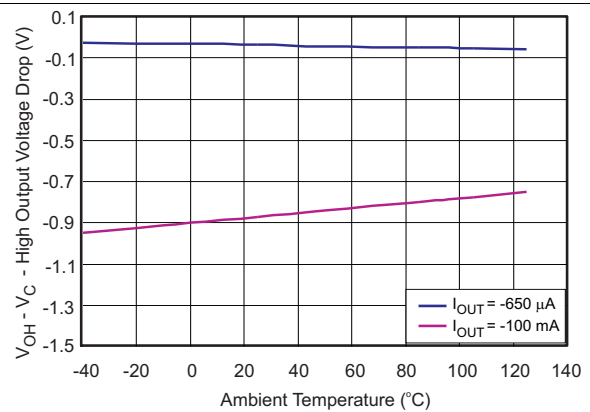


Figure 10. High Output Voltage Drop vs. Temperature

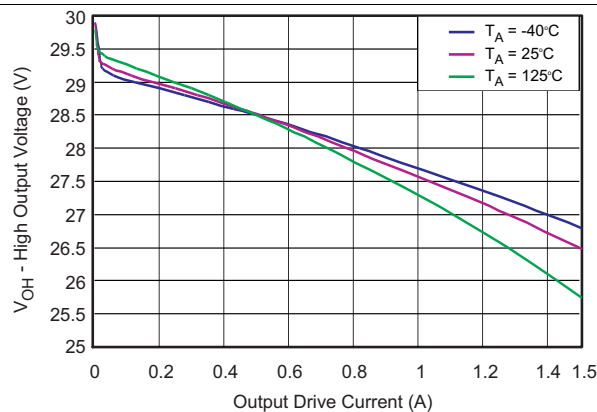


Figure 11. High Output Voltage vs. Output Drive Current

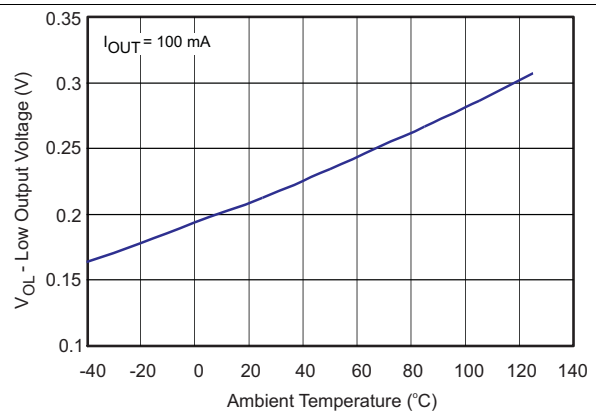


Figure 12. Low Output Voltage vs. Temperature

Typical Characteristics (continued)

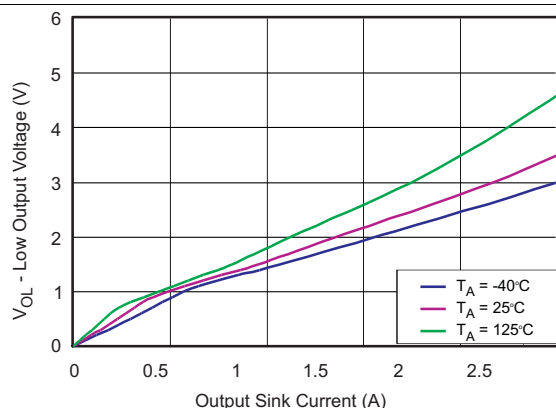


Figure 13. Low Output Voltage vs. Output Sink Current

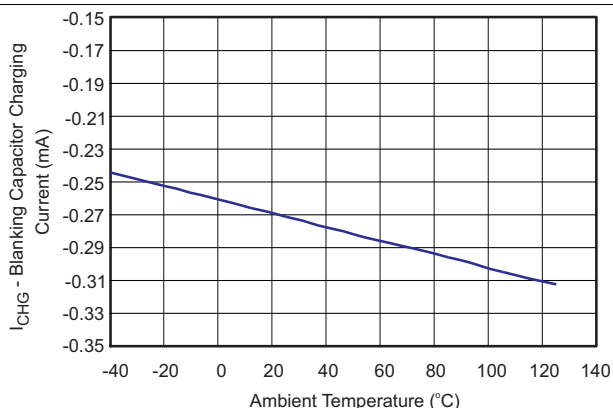


Figure 14. Blanking Capacitance Charging Current vs. Temperature

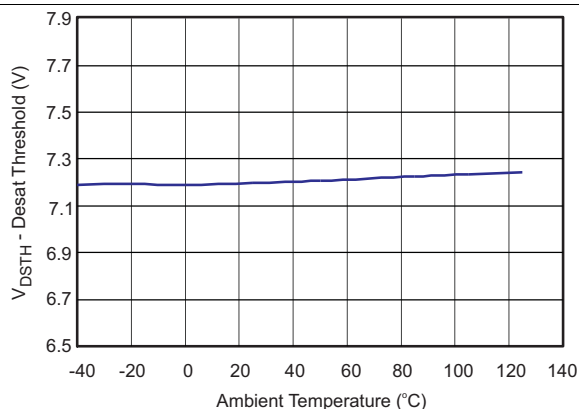


Figure 15. DESAT Threshold vs. Temperature

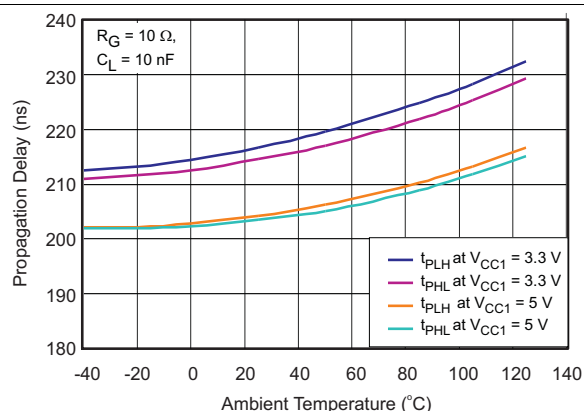


Figure 16. Propagation Delay vs. Temperature

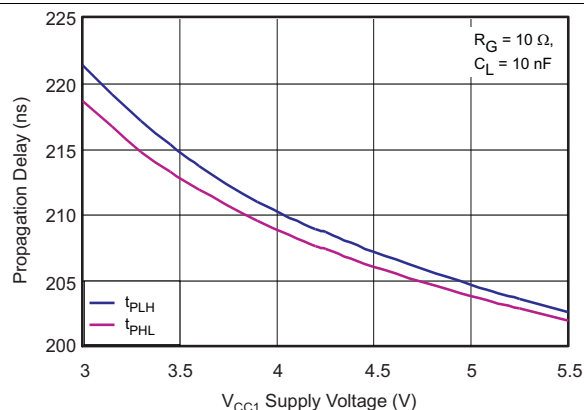


Figure 17. Propagation Delay vs. V_{CC1} Supply Voltage

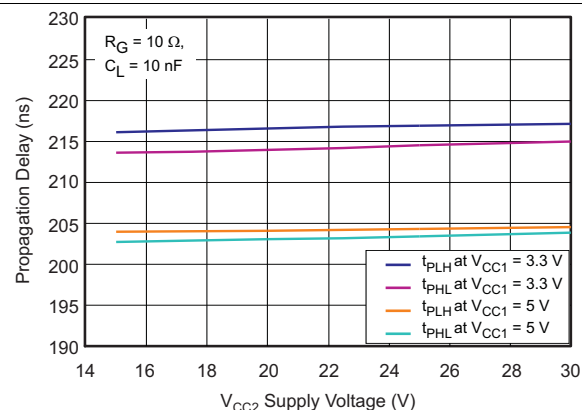


Figure 18. Propagation Delay vs. V_{CC2} Supply Voltage

Typical Characteristics (continued)

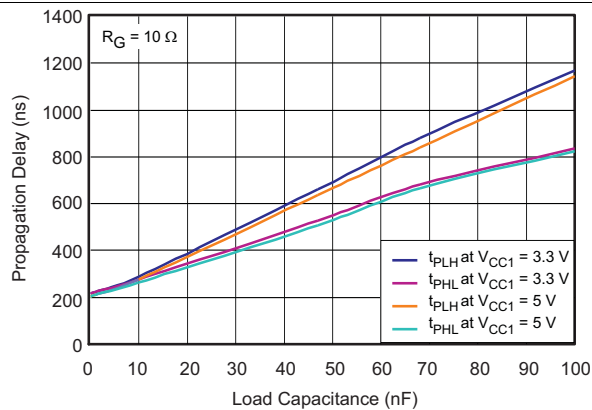


Figure 19. Propagation Delay vs. Load Capacitance

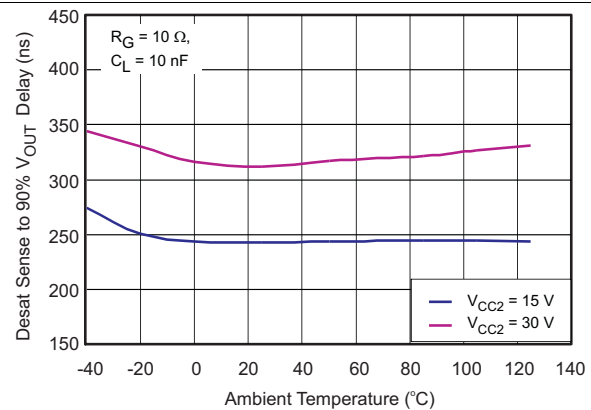


Figure 20. DESAT Sense to 90% V_{OUT} Delay vs Temperature

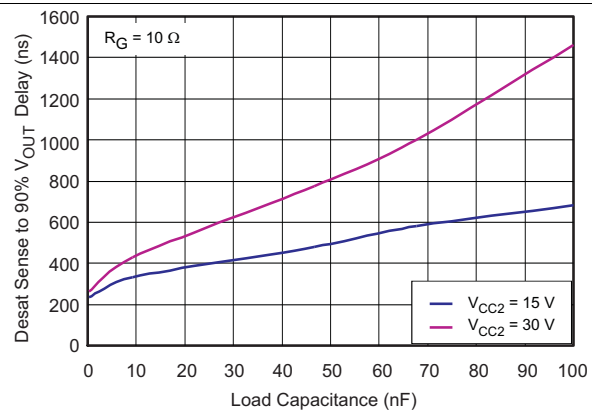


Figure 21. DESAT Sense to 90% V_{OUT} Delay vs Load Capacitance

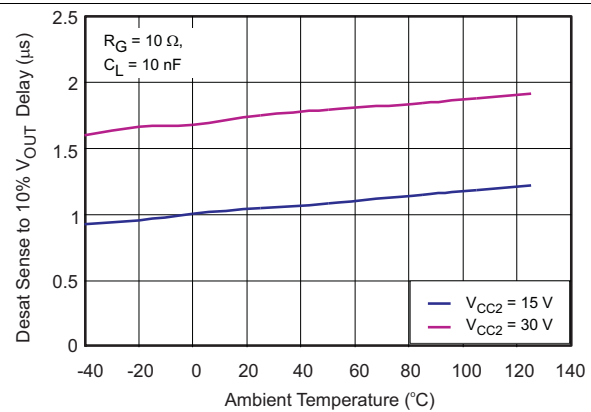


Figure 22. DESAT Sense to 10% V_{OUT} Delay vs Temperature

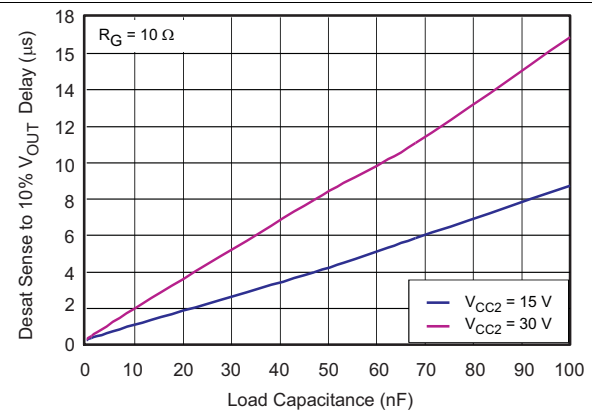


Figure 23. DESAT Sense to 10% V_{OUT} Delay vs Load Capacitance

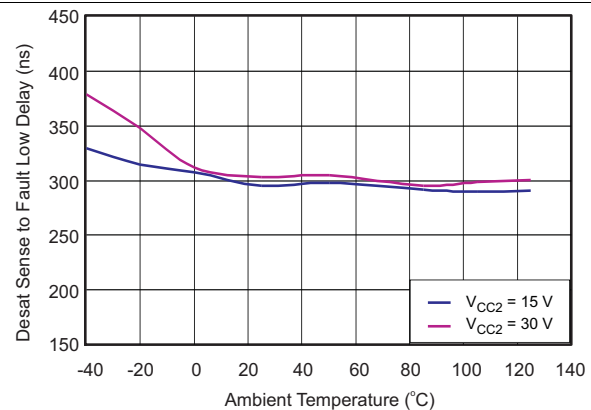


Figure 24. DESAT Sense to Fault Low Delay vs Temperature

Typical Characteristics (continued)

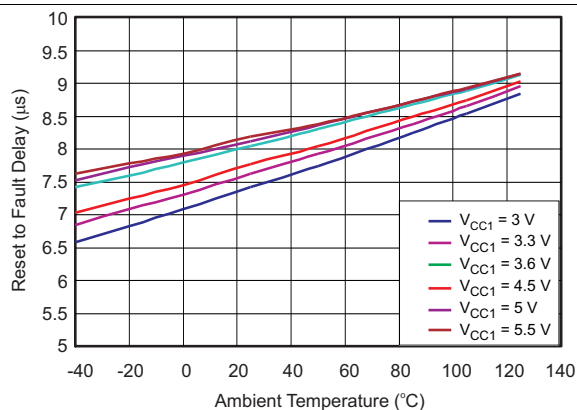


Figure 25. Reset to Fault Delay vs Temperature

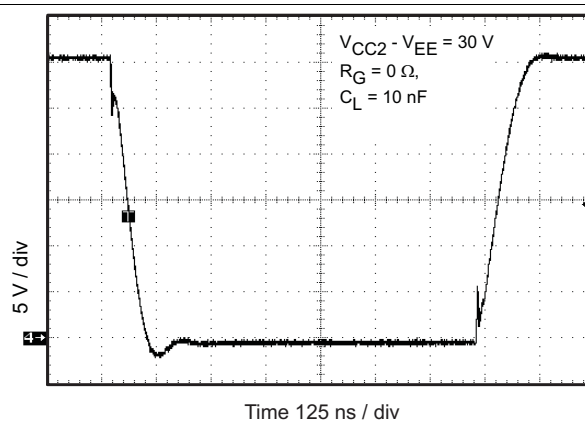


Figure 26. Output Waveform

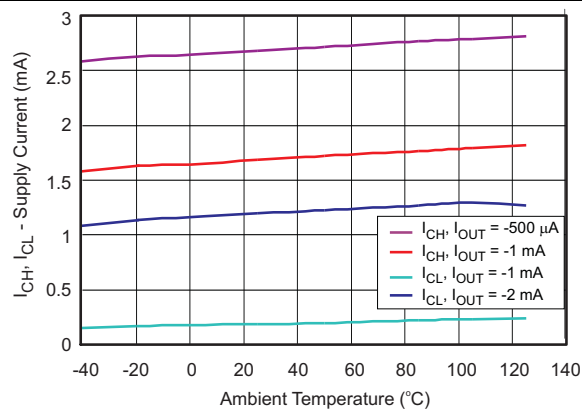


Figure 27. V_C Supply Current vs. Temperature

Parameter Measurement Information (continued)

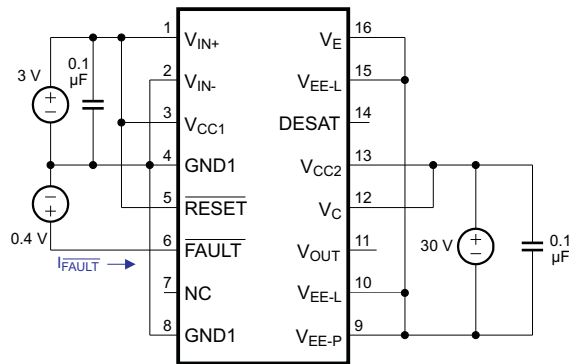


Figure 34. I_{FL} Test Circuit

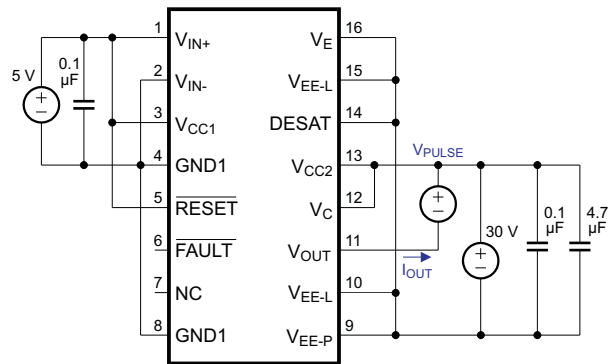


Figure 35. I_{OH} Test Circuit

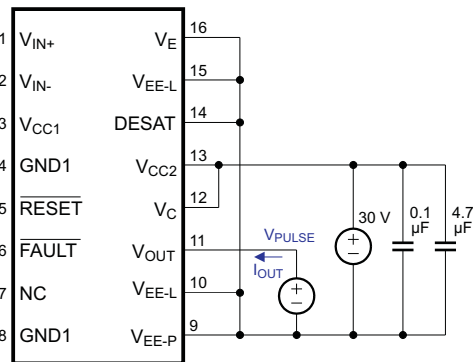


Figure 36. I_{OL} Test Circuit

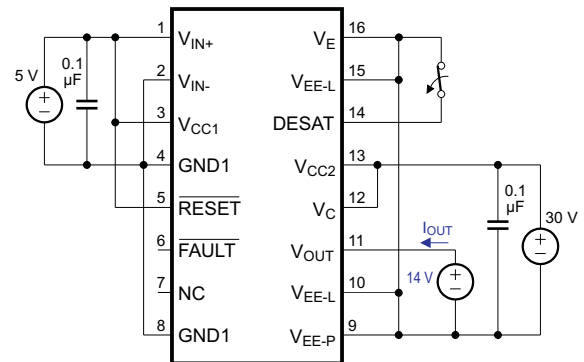


Figure 37. I_{OF} Test Circuit

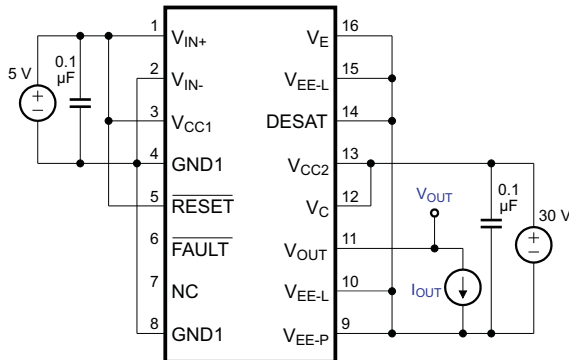


Figure 38. V_{OH} Test Circuit

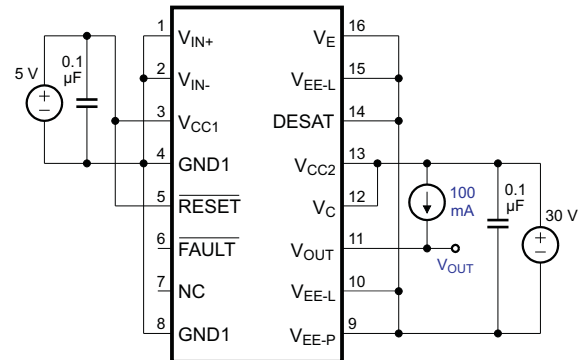
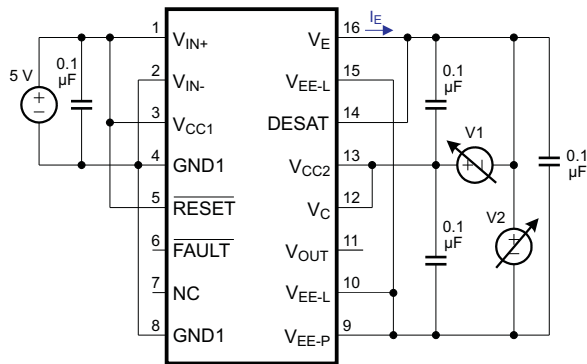
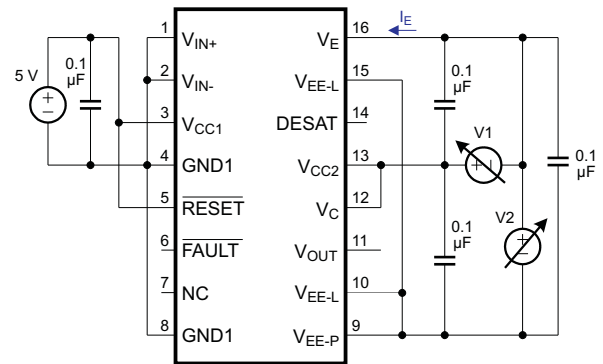
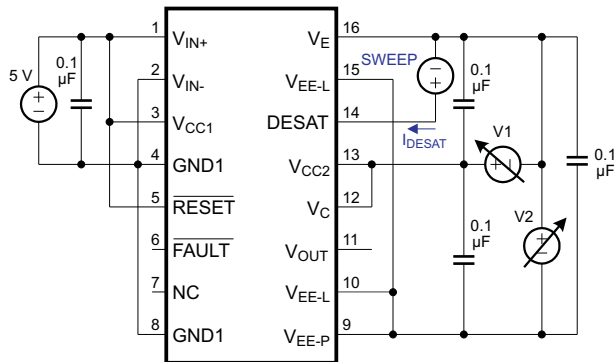
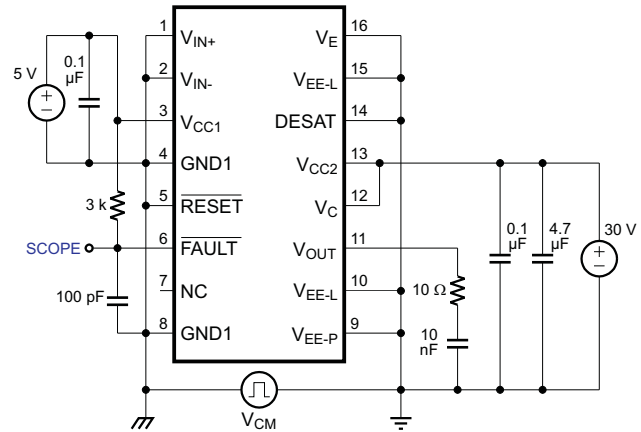
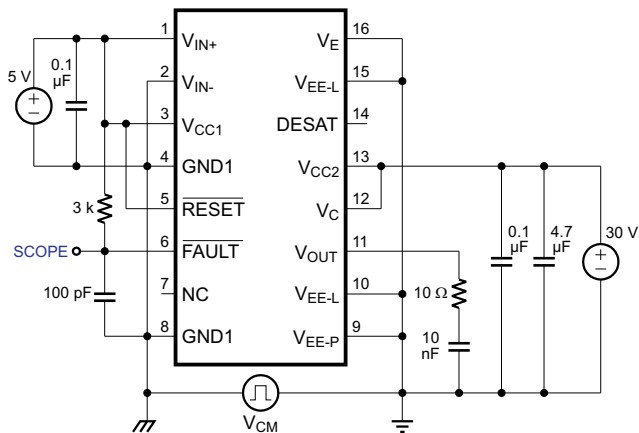
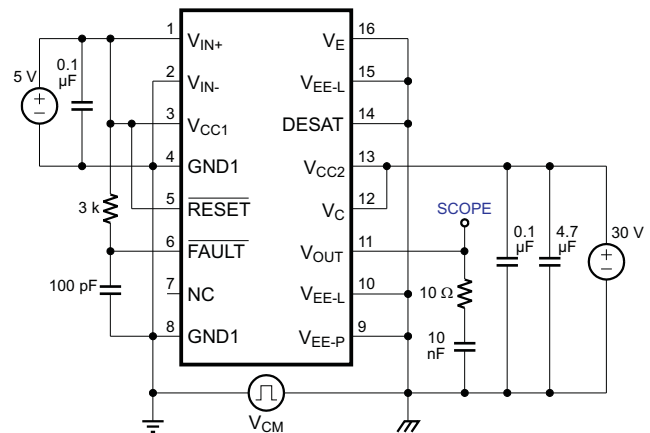


Figure 39. V_{OL} Test Circuit

Parameter Measurement Information (continued)

Figure 40. I_{EH} Test Circuit

Figure 41. I_{EL} Test Circuit

Figure 42. I_{CHG} , I_{DSCHG} , V_{DSTH} Test Circuit

Figure 43. CMTI V_{FH} Test Circuit

Figure 44. CMTI V_{FL} Test Circuit

Figure 45. CMTI V_{OH} Test Circuit

Parameter Measurement Information (continued)

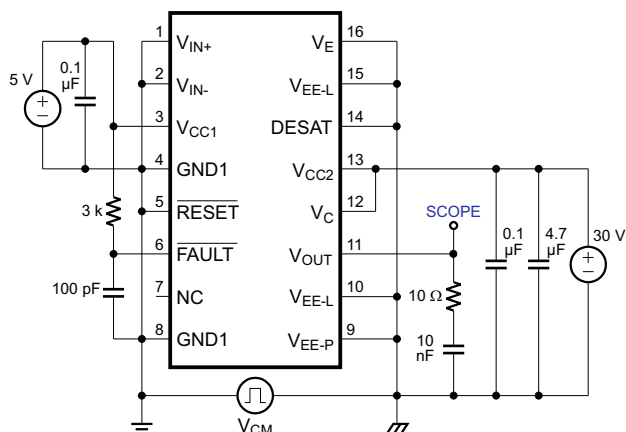


Figure 46. CMTI V_{OL} Test Circuit

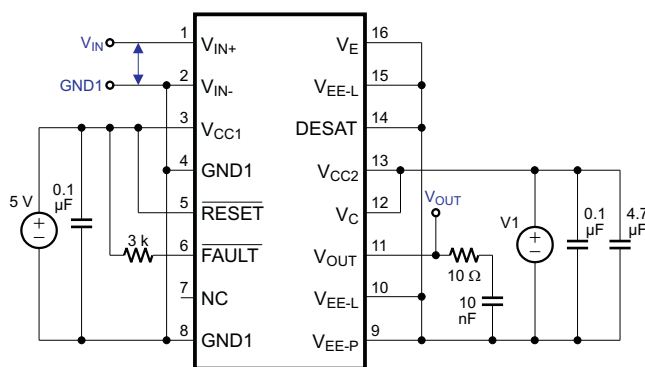


Figure 47. t_{PLH} , t_{PHL} , t_r , t_f Test Circuit

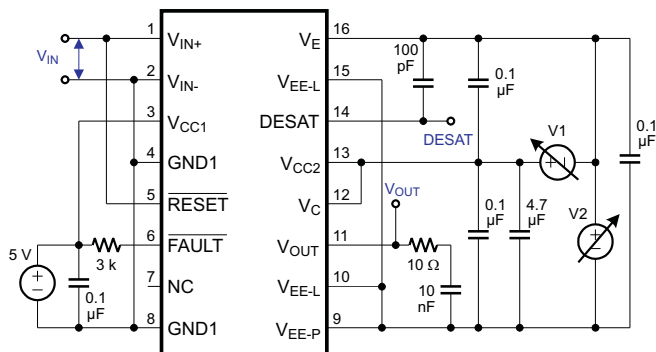


Figure 48. t_{DESAT} , t_{RESET} Test Circuit

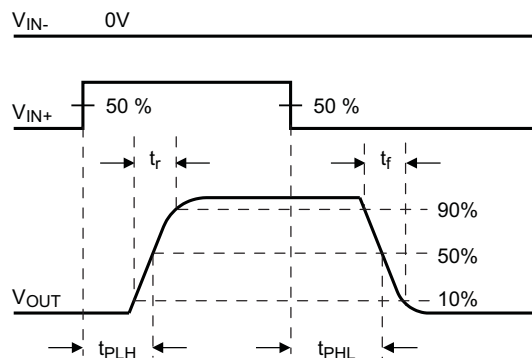


Figure 49. V_{OUT} Propagation Delay, Non-inverting Configuration

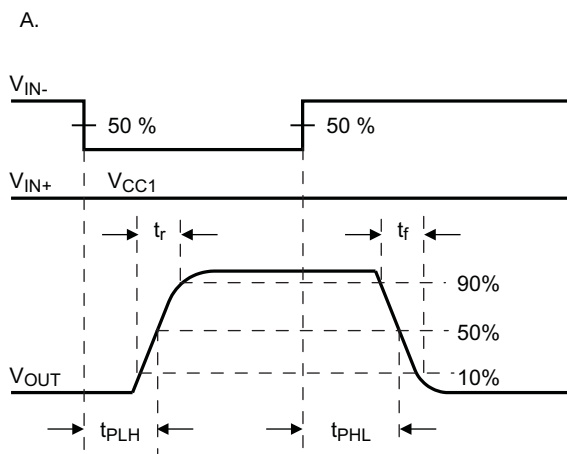


Figure 50. V_{OUT} Propagation Delay, Inverting Configuration

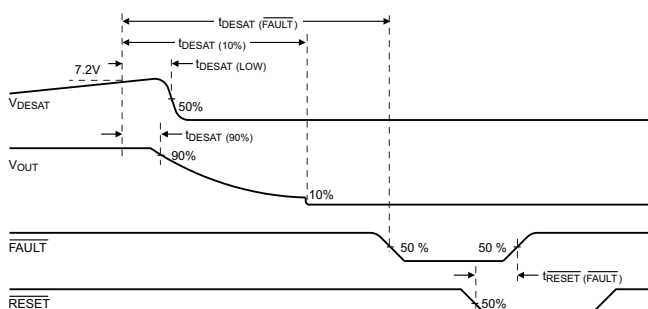


Figure 51. $DESAT$, V_{OUT} , $FAULT$, $RESET$ Delays

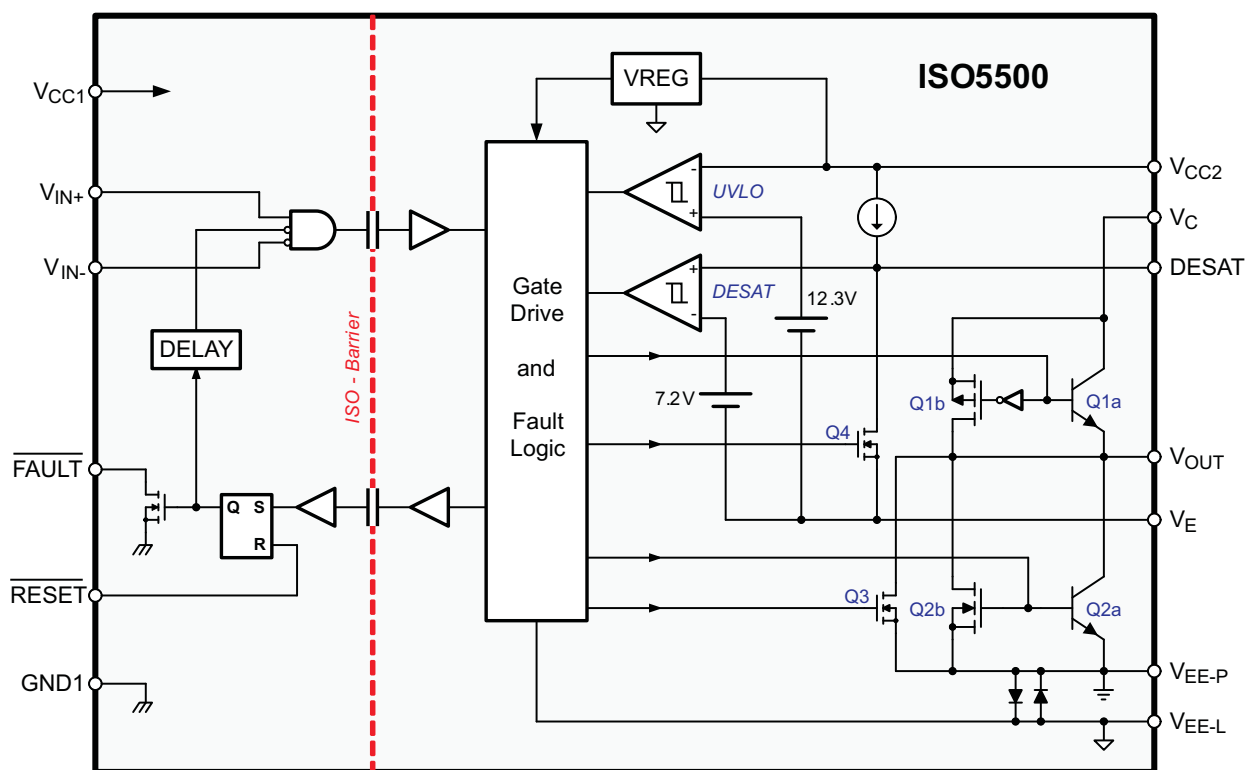
8 Detailed Description

8.1 Overview

The ISO5500 is an isolated gate driver for IGBTs and MOSFETs with power ratings of up to $I_C = 150\text{ A}$ and $V_{CE} = 600\text{ V}$. Input TTL logic and output power stage are separated by a capacitive, silicon dioxide (SiO_2), isolation barrier.

The IO circuitry on the input side interfaces with a micro controller and consists of gate drive control and $\overline{\text{RESET}}$ inputs, and $\overline{\text{FAULT}}$ alarm output. The power stage consists of power transistors to supply 2.5 A pullup and pulldown currents to drive the capacitive load of the external power transistors, as well as DESAT detection circuitry to monitor IGBT collector-emitter overvoltage under short circuit events. The capacitive isolation core consists of transmit circuitry to couple signals across the capacitive isolation barrier, and receive circuitry to convert the resulting low-swing signals into CMOS levels. The ISO5500 also contains undervoltage lockout circuitry to prevent insufficient gate drive to the external IGBT, and soft turnoff feature which ensures graceful reduction in IGBT current to zero when a short-circuit is detected.

8.2 Functional Block Diagram



8.3 Feature Description

Table 1. Package Characteristics

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$L_{(I01)}$ Minimum air gap (clearance ⁽¹⁾)	Shortest terminal to terminal distance through air	8.3			mm
$L_{(I02)}$ Minimum external tracking (creepage ⁽¹⁾)	Shortest terminal to terminal distance across the package surface	8.1			mm
	Minimum internal gap (internal clearance)	Distance through the insulation	0.012		mm
CTI Tracking resistance (comparative tracking index)	DIN IEC 60112 / VDE 0303 Part 1	400			V
R_{IO} Isolation resistance	Input to output, $V_{IO} = 500 \text{ V}^{(2)}$	$>10^{12}$			Ω
C_{IO} Barrier capacitance input-to-output	$V_{IO} = 0.4 \sin(2\pi ft)$, $f = 1 \text{ MHz}^{(2)}$		1.25		pF
C_i Input capacitance to ground	$V_i = V_{CC}/2 + 0.4 \sin(2\pi ft)$, $f = 2 \text{ MHz}$, $V_{CC} = 5 \text{ V}$		2		pF

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board do not reduce this distance.

Creepage and clearance on a printed circuit board become equal according to the measurement techniques shown in the isolation glossary. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase their specification.

- (2) All pins on each side of the barrier tied together creating a two-terminal device

8.3.1 Insulation Characteristics for DW-16 Package

Over recommended operating conditions (unless noted otherwise)

PARAMETER	TEST CONDITIONS	SPECIFICATION	UNIT
V_{IORM} Maximum working insulation voltage per DIN V VDE V 0884-10 (VDE V 0884-10)		679/480	V_{PEAK}/V_{RMS}
V_{PR} Input to output test voltage per DIN V VDE V 0884-10 (VDE V 0884-10)	After Input/Output safety test subgroup 2/3, $V_{PR} = 1.2 \times V_{IORM}$, $t = 10 \text{ sec}$, Partial discharge $< 5 \text{ pC}$	816/576	
	Method a, After environmental tests subgroup 1, $V_{PR} = 1.6 \times V_{IORM}$, $t = 10 \text{ sec}$ (qualification) Partial discharge $< 5 \text{ pC}$	1088/768	
	Method b1, 100% Production test, $V_{PR} = 1.875 \times V_{IORM}$, $t = 1 \text{ sec}$ Partial discharge $< 5 \text{ pC}$	1275/900	
V_{IOTM} Transient overvoltage per DIN V VDE V 0884-10 (VDE V 0884-10)	$V_{TEST} = V_{IOTM}$, $t = 60 \text{ sec}$ (qualification), $t = 1 \text{ sec}$ (100% production)	6000/4243	
V_{ISO} Isolation voltage per UL 1577	$V_{TEST} = V_{ISO}$, $t = 60 \text{ sec}$ (qualification)	6000/4243	Ω
	$V_{TEST} = 1.2 \times V_{ISO}$, $t = 1 \text{ sec}$ (100% production)	7200/5092	
R_S Insulation resistance	$V_{IO} = 500 \text{ V}$ at $T_S = 150^\circ\text{C}$	$> 10^9$	
Pollution degree		2	

8.3.2 Regulatory Information

VDE	CSA	UL
Certified according to DIN V VDE V 0884-10 (VDE V 0884-10)	Approved under CSA Component Acceptance Notice 5A	Recognized under 1577 Component Recognition Program
Basic Insulation Maximum Transient Overvoltage, 6000 V_{PK} Maximum Working Voltage, 680 V_{PK}	Basic and Reinforced Insulation per CSA 60950-1-07 and IEC 60950-1 (2nd Ed)	Single Protection, 4243 $V_{RMS}^{(1)}$
Certificate Number: 40016131	Master Contract Number: 220991	File Number: E181974

- (1) Production tested $\geq 5092 \text{ V}_{RMS}$ for 1 second in accordance with UL 1577.

8.3.3 IEC 60664-1 Rating Table

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic Isolation Group	Material Group	II
Installation Classification	Rated Mains Voltage $\leq 300 V_{RMS}$	I-IV
	Rated Mains Voltage $\leq 600 V_{RMS}$	I-III

8.3.4 Isolation Lifetime at a Maximum Continuous Working Voltage

PARAMETER	LIFETIME	SPECIFICATION	UNIT
Bipolar AC Voltage	20 years	679/480	V_{PEAK}/V_{RMS}
	25 years	657/465	
	50 years	601/425	

8.3.5 Safety Limiting Values

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_S Safety Limiting Current	$\theta_{JA} = 76^\circ\text{C/W}$, $V_I = 3.6\text{ V}$, $T_J = 170^\circ\text{C}$, $T_A = 25^\circ\text{C}$			530	mA
	$\theta_{JA} = 76^\circ\text{C/W}$, $V_I = 5.5\text{ V}$, $T_J = 170^\circ\text{C}$, $T_A = 25^\circ\text{C}$			347	
	$\theta_{JA} = 76^\circ\text{C/W}$, $V_I = 30\text{ V}$, $T_J = 170^\circ\text{C}$, $T_A = 25^\circ\text{C}$			64	
T_S Case Temperature				150	$^\circ\text{C}$

The safety-limiting constraint is the absolute-maximum junction temperature specified in the [Absolute Maximum Ratings](#) table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the [Thermal Information](#) table is that of a device installed in the High-K Test Board for Leaded Surface-Mount Packages. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

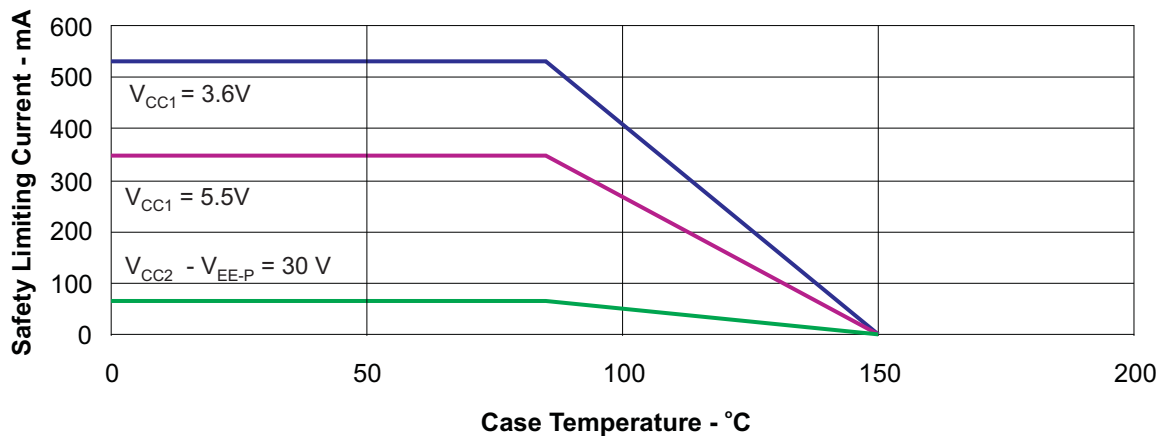


Figure 52. DW-16 θ_{JC} Thermal Derating Curve per DIN V VDE V 0884-10 (VDE V 0884-10)

8.3.6 Behavioral Model

Figure 53 and Figure 54 show the detailed behavioral model of the ISO5500 for a non-inverting input configuration and its corresponding timing diagram for normal operation, fault condition, and Reset.

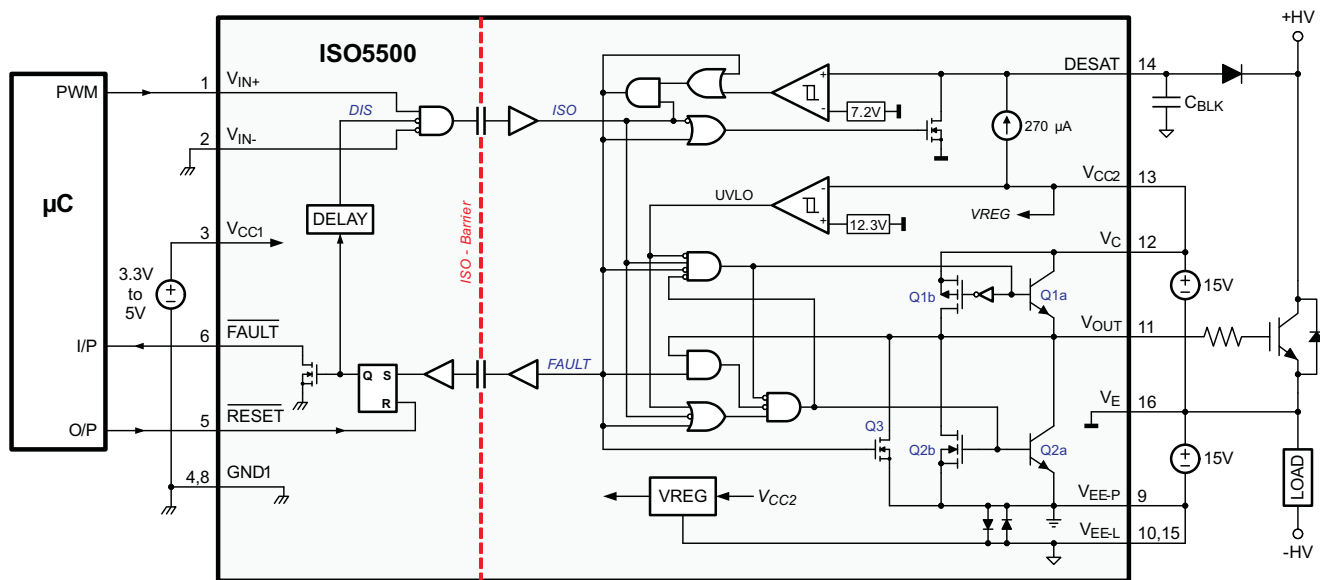


Figure 53. ISO5500 Behavioral Model

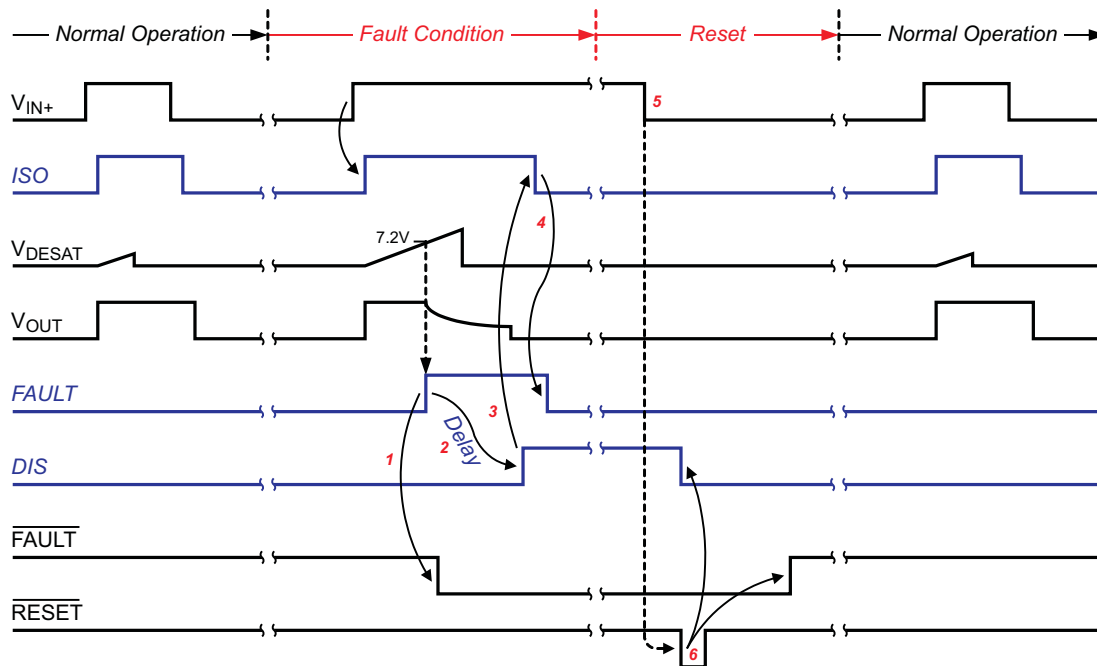


Figure 54. Complete Timing Diagram

8.3.7 Power Supplies

V_{CC1} and GND1 are the power supply input and output for the input side of the ISO5500. The supply voltage at V_{CC1} can range from 3 V up to 5.5 V with respect to GND1, thus supporting the direct interface to state-of-the-art 3.3 V low-power controllers as well as legacy 5 V controllers.

V_{CC2} , V_{EE-P} and V_{EE-L} are the power supply input and supply returns for the output side of the ISO5500. V_{EE-P} is the supply return for the output driver and V_{EE-L} is the return for the logic circuitry. With V_{EE-P} as the main reference potential, V_{EE-L} should always be directly connected to V_{EE-P} . The supply voltage at V_{CC2} can range from 15 V up to 30 V with respect to V_{EE-P} .

A third voltage input, V_E , serves as reference voltage input for the internal UVLO and DESAT comparators. V_E also represents the common return path for the gate voltage of the external power device. The ISO5500 is designed for driving MOSFETs and IGBTs. Because MOSFETs do not require a negative gate-voltage, the voltage potential at V_E with respect to V_{EE-P} can range from 0 V for MOSFETs and up to 15 V for IGBTs.

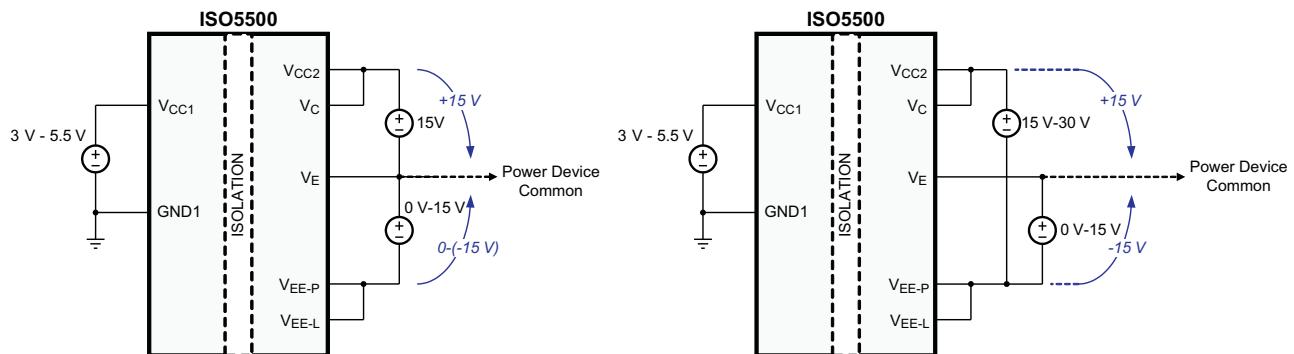


Figure 55. Power Supply Configurations

The output supply configuration on the left uses symmetrical ± 15 V supplies for V_{CC2} and V_{EE-P} with respect to V_E . This configuration is mostly applied when deriving the output supply from the input supply via an isolated DC-DC converter with symmetrical voltage outputs. The configuration on the right, having both supplies referenced to V_{EE-P} , is found in applications where the device output supply is derived from the high-voltage IGBT supplies.

8.3.8 Control Signal Inputs

The two digital, TTL control inputs, V_{IN+} and V_{IN-} , allow for inverting and non-inverting control of the gate driver output. In the non-inverting configuration V_{IN+} receives the control input signal and V_{IN-} is connected to GND1. In the inverting configuration V_{IN-} is the control input while V_{IN+} is connected to V_{CC1} .

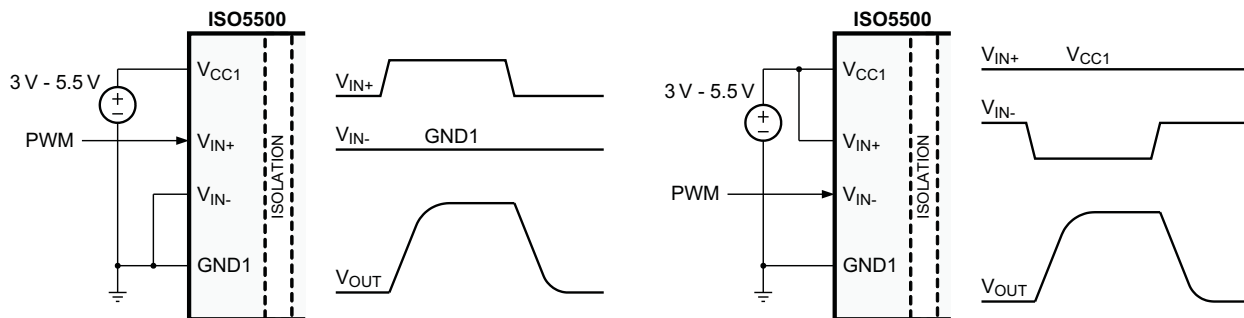


Figure 56. Non-inverting (left) and Inverting (right) Input Configurations

8.3.9 Output Stage

The output stage provides the actual IGBT gate drive by switching the output voltage pin, V_{OUT} , between the most positive potential, typically V_{CC2} , and the most negative potential, V_{EE-P} .

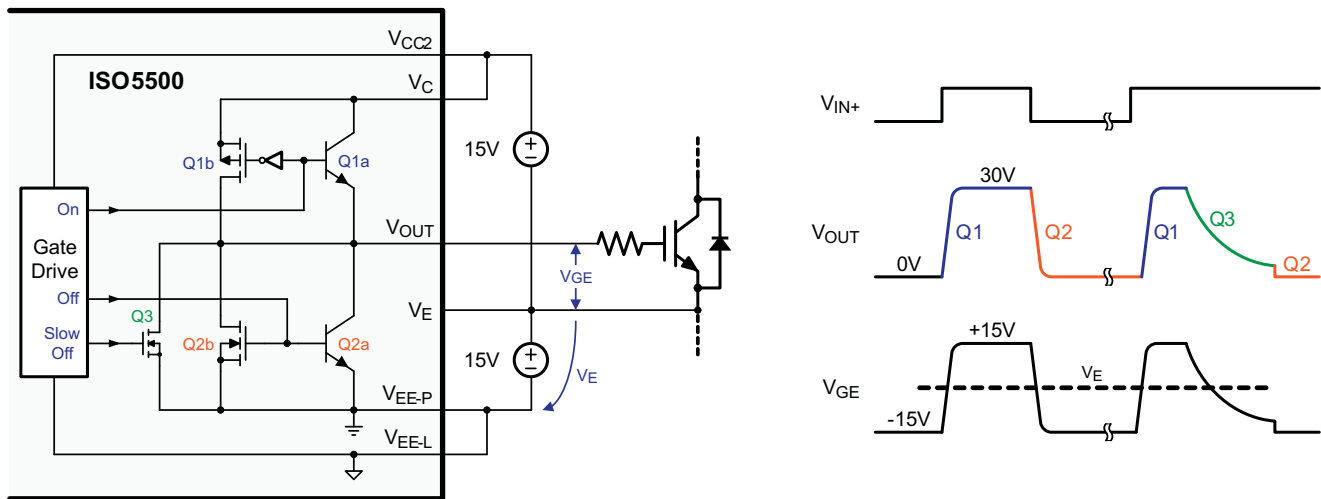


Figure 57. Output Stage Design and Timing

This stage consists of an upper transistor pair (Q1a and Q1b) turning the IGBT on, and a lower transistor pair (Q2a and Q2b) turning the IGBT off. Each transistor pair possesses a bipolar transistor for high current drive and a MOSFET for close-to-rail switching capability.

An additional, weak MOSFET (Q3) is used to softly turn-off the IGBT in the event of a short circuit fault to prevent large di/dt voltage transients which potentially could damage the output circuitry.

The output control signals, On, Off, and Slow-Off are provided by the gate-drive and fault-logic circuit which also includes a break-before-make function to prevent both transistor pairs from conducting at the same time.

By introducing the reference potential for the IGBT emitter, V_E , the final IGBT gate voltage, V_{GE} , assumes positive and negative values with respect to V_E .

A positive V_{GE} of typically 15 V is required to switch the IGBT well into saturation while assuring the survival of short circuit currents of up to 5–10 times the rated collector current over a time span of up to 10 μ s.

Negative values of V_E , ranging from a required minimum of –5 V up to a recommended –15 V, are necessary to keep the IGBT turned off and to prevent it from unintentional conducting due to noise transients, particularly during short circuit faults. As previously mentioned, MOSFETs do not require a negative gate-voltage and thus allow the V_{E-P} pin to be directly connected to V_{EE-P} .

The timing diagram in Figure 57 shows that during normal operation V_{OUT} follows the switching sequence of V_{IN+} (here shown for the non-inverting input configuration), and only the Q1 and Q2 transistor pairs applying V_{CC2} and V_{EE-P} potential to the V_{OUT} -pin respectively.

In the event of a short circuit fault, however, while the IGBT is actively driven, the Q1 pair is turned off and Q3 turns on to slowly reduce V_{OUT} in a controlled manner down to a level of approximately 2 V above V_{EE-P} . At this voltage level, the strong Q2 pair then conducts holding V_{OUT} at V_{EE-P} potential.

8.3.10 Undervoltage Lockout (UVLO)

The Under Voltage Lockout feature prevents the application of insufficient gate voltage (V_{GE-ON}) to the power device by forcing V_{OUT} low ($V_{OUT} = V_{EE-P}$) during power-up and whenever else $V_{CC2} - V_E$ drops below 12.3 V.

IGBTs and MOSFETs typically require gate voltages of $V_{GE} = 15$ V to achieve their rated, low saturation voltage, V_{CES} . At gate voltages below 13 V typically, their V_{CE-ON} increases drastically, especially at higher collector currents. At even lower voltages, i.e. $V_{GE} < 10$ V, an IGBT starts operating in the linear region and quickly overheats. Figure 58 shows the principle operation of the UVLO feature.

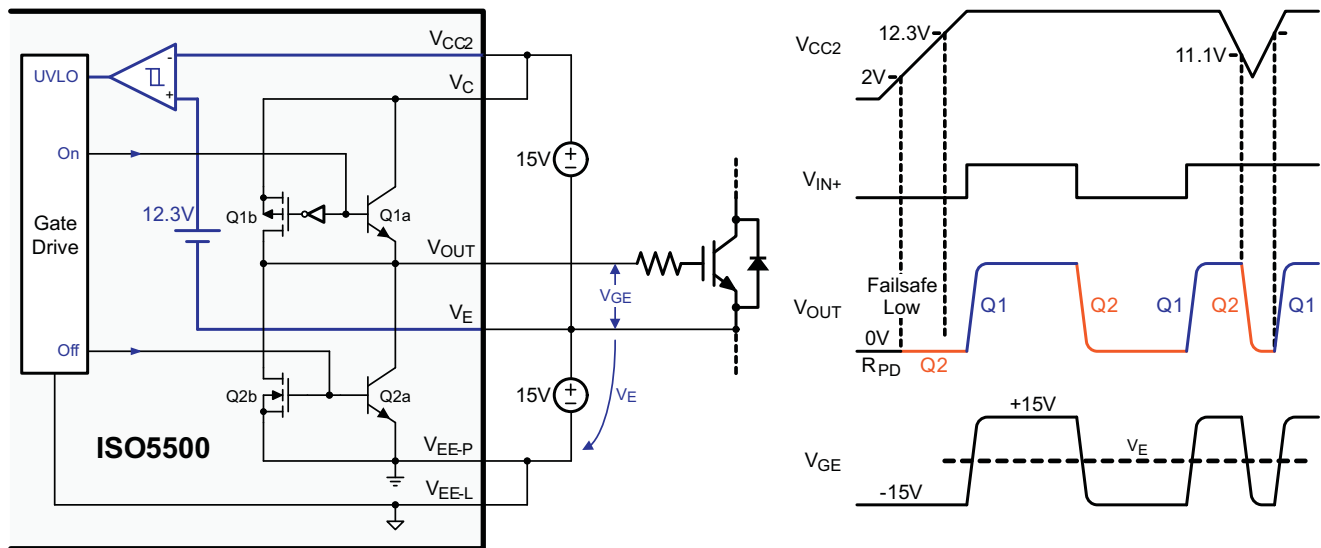


Figure 58. Undervoltage Lockout (UVLO) Function

Because V_{CC2} with respect to V_E represents the gate-on voltage, $V_{GE-ON} = V_{CC2} - V_E$, the UVLO comparator compares V_{CC2} to a 12.3 V reference voltage that is also referenced to V_E via the connection of the ISO5500 V_{E-} pin to the emitter potential of the power device.

The comparator hysteresis is 1.2 V typical and the typical values for the positive and negative going input threshold voltages are $V_{TH+} = 12.3$ V and $V_{TH-} = 11.1$ V.

The timing diagram shows that at V_{CC2} levels below 2 V V_{OUT} is 0 V. Because none of the internal circuitry operates at such low supply levels, an internal 100 k Ω pull-down resistor is used to pull V_{OUT} down to V_{EE-P} potential. This initial weak clamping, known as failsafe-low output, strengthens with rising V_{CC2} . Above 2 V the Q2-pair starts conducting gradually until V_{CC2} reaches 12.3 V at which point the logic states of the control inputs V_{IN+} and V_{IN-} begin to determine the state of V_{OUT} .

Another UVLO event takes place should V_{CC2} drop slightly below 11 V while the IGBT is actively driven. At that moment the UVLO comparator output causes the gate-drive logic to turn off Q1 and turn on Q2. Now V_{OUT} is clamped hard to V_{EE-P} . This condition remains until V_{CC2} returns to above 12.3 V and normal operation commences.

NOTE

An Undervoltage Lockout does not indicate a Fault condition.

8.3.11 Desaturation Fault Detection (DESAT)

The DESAT fault detection prevents IGBT destruction due to excessive collector currents during a short circuit fault. Short circuits caused by user misconnect, bad wiring, or overload conditions induced by the load can cause a rapid increase in IGBT current, leading to excessive power dissipation and heating. IGBTs become damaged when the current load approaches the saturation current of the device and the collector-emitter voltage, V_{CE} , rises above the saturation voltage level, V_{CE-sat} . The drastically increased power dissipation overheats and destroys the IGBT.

To prevent damage to IGBT applications, the implemented fault detection slowly reduces the overcurrent in a controlled manner during the fault condition.



At the same time the fault logic turns off the power-pair Q1 and turns on the small discharge MOSFETs, Q3 and Q4. Q3 slowly discharges the IGBT gate voltage which causes the high short-circuit current through the IGBT to gradually decrease, thereby preventing large di/dt induced voltage transients. Q4 discharges the blanking capacitor. Once V_{OUT} is sufficiently close to V_{EE-P} potential (at approximately 2 V), the large Q2-pair turns on in addition to Q3 to clamp the IGBT gate to V_{FF-P} .

The DESAT detection circuit is only active when the IGBT is turned on. When the IGBT is turned off, and its V_{CE} is at maximum, the fault detection is simply disabled to prevent false triggering of fault signals.

$$t_{\text{BLK}} = \frac{C_{\text{BLK}} \times V_{\text{DSTH}}}{I_{\text{CHG}}} = \frac{100 \text{ pF} \times 7.2 \text{ V}}{270 \text{ }\mu\text{A}} = 2.7 \text{ }\mu\text{s} \quad (1)$$

If a short circuit condition exists prior to the turn-on of the IGBT, (*causing the IGBT switching into a short*) the soft shutdown sequence begins after approximately 3 μ s. However, if a short circuit condition occurs while the IGBT is already on, the response time is significantly shorter due to the parasitic parallel capacitance of the DESAT diode. The recommended value of 100 pF however, provides sufficient blanking and fault response times for most applications.

The timing diagram in [Figure 59](#) shows the DESAT function for both, normal operation and a short-circuit fault condition. The use of V_{IN+} as control input implies non-inverting input configuration.

During normal operation V_{DESAT} will display a small sawtooth waveform every time V_{IN+} goes high. The ramp of the sawtooth is caused by the internal current source charging the blanking capacitor. Once the IGBT collector has sufficiently dropped below the capacitor voltage, the DESAT diode conducts and discharges C_{BLK} through the IGBT.

In the event of a short circuit fault; however, high IGBT collector voltage prevents the diode from conducting and the voltage at the blanking capacitor continues to rise until it reaches the DESAT threshold. When the output of the DESAT comparator goes high, the gate-drive and fault-logic circuit initiates the soft shutdown sequence and also produces a Fault signal that is fed back to the input side of the ISO5500.

8.3.13 $\overline{\text{FAULT}}$ Alarm

The Fault alarm unit consists of three circuit elements, a RS flip-flop to store the fault signal received from the gate-drive and fault-logic, an open-drain MOSFET output signaling the fault condition to the micro controller, and a delay circuit blocking the control inputs after the soft shutdown sequence of the IGBT has been completed.

[Figure 60](#) shows the ISO5500 in a non-inverting input configuration. Because the $\overline{\text{FAULT}}$ -pin is an open-drain output, it requires a pull-up resistor, R_{PU} , in the order of 3.3 k Ω to 10 k Ω . The internal signals DIS, ISO, and FAULT represent the input-disable signal, the isolator output signal, and the fault feedback signal respectively.

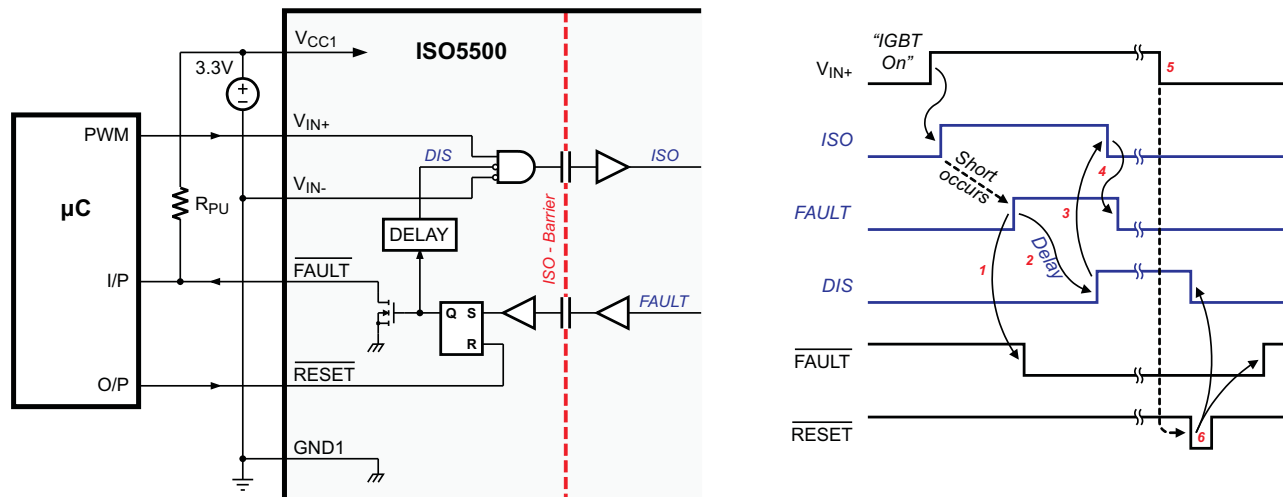


Figure 60. Fault Alarm Circuitry and Timing Sequence

The timing diagram shows that the micro controller initiates an IGBT-on command by taking V_{IN+} high. After propagating across the isolation barrier ISO goes high, activating the output stage.

1. Upon a short circuit condition the gate-drive and fault-logic feeds back a fault signal ($\text{FAULT} = \text{high}$) which sets the RS-FF driving the $\overline{\text{FAULT}}$ output active-low.
2. After a delay of approximately 3 μs , the time required to shutdown the IGBT, DIS becomes high and blocks the control inputs
3. This in turn drives ISO low
4. which, after propagating through the output fault-logic, drives FAULT low.

At this time both flip-flop inputs are low and the fault signal is stored.

5. Once the failure cause has been removed the micro controller must set the control inputs into an "Output-low" state before applying the Reset pulse.
6. Taking the $\overline{\text{RESET}}$ -input low resets the flip-flop, which removes the fault signal from the controller by pulling $\overline{\text{FAULT}}$ high and releases the control inputs by driving DIS low

8.4 Device Functional Modes

Table 2. Function Table

V_{IN+}	V_{IN-}	UVLO ($V_{CC2} - V_E$)	DESAT DETECTED ON PIN 14 (DESAT)	PIN 6 (FAULT) OUTPUT	V_{OUT}
X	X	Active	X	X	Low
X	X	X	Yes	Low	Low
Low	X	X	X	X	Low
X	High	X	X	X	Low
High	Low	Not active	No	High	High

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The ISO5500 is an isolated gate driver for high power devices such as IGBTs and MOSFETs with power ratings of up to $I_C = 150\text{ A}$ and $V_{CE} = 600\text{ V}$. It is intended for use in applications such as motor control, industrial inverters and switched-mode power supplies. In these applications, sophisticated PWM control signals are required to turn the power-devices on and off, which at the system level eventually may determine, for example, the speed, position, and torque of the motor or the output voltage, frequency and phase of the inverter. These control signals are usually the outputs of a micro controller, and are at low voltage levels such as 3.3 V or 5.0 V. The gate controls required by the MOSFETs and IGBTs, on the other hand, are in the range of 15 V to 30 V, and need high current capability to be able to drive the large capacitive loads offered by those power transistors. Not only that, the gate drive needs to be applied with reference to the Emitter of the IGBT (Source for MOSFET), and by construction, the Emitter node in a gate drive system swings between 0 to the DC bus voltage, which is several 100s of volts in magnitude.

The ISO5500 is thus used to level shift the incoming 3.3-V and 5.0-V control signals from the microcontroller to the 15-V to 30-V drive required by the power transistors while ensuring high-voltage isolation between the driver side and the microcontroller side.

9.2 Typical Application

Figure 61 shows the typical application of a three-phase inverter using six ISO5500 isolated gate drivers. Three-phase inverters are used for variable-frequency drives to control the operating speed of AC motors and for high power applications such as High-Voltage DC (HVDC) power transmission.

The basic three-phase inverter consists of three single-phase inverter switches each comprising two ISO5500 devices that are connected to one of the three load terminals. The operation of the three switches is coordinated so that one switch operates at each 60 degree point of the fundamental output waveform, thus creating a six-step line-to-line output waveform. In this type of applications carrier-based PWM techniques are applied to retain waveform envelope and cancel harmonics.

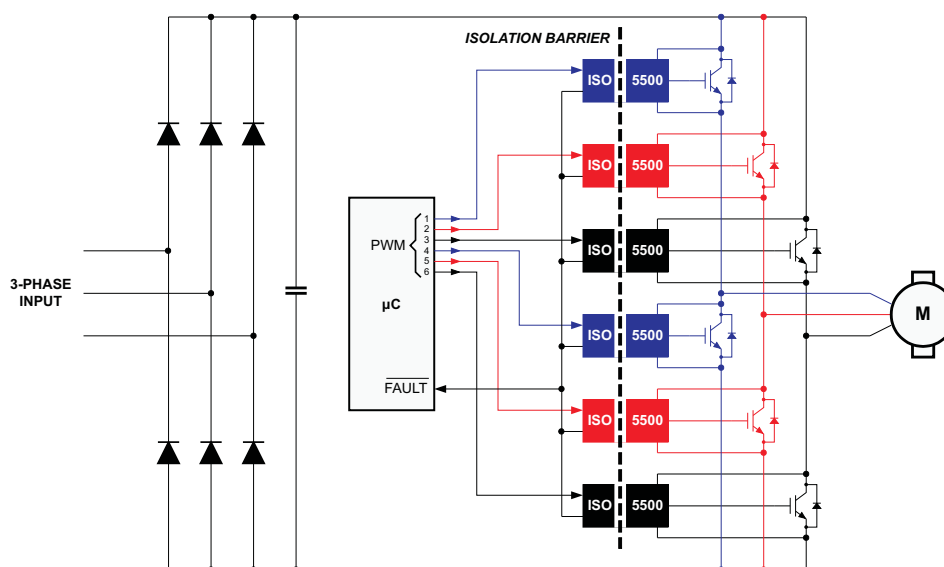


Figure 61. Typical Motor Drive Application

Typical Application (continued)

9.2.1 Design Requirements

Unlike optocoupler based gate drivers which need external current drivers and biasing circuitry to provide the input control signals, the input control to the ISO5500 is TTL and can be directly driven by the microcontroller. Other design requirements include decoupling capacitors on the input and output supplies, a pullup resistor on the common drain $\overline{\text{FAULT}}$ output signal, and a high-voltage protection diode between the IGBT collector and the DESAT input. Further details are explained in the subsequent sections.

9.2.2 Detailed Design Procedure

9.2.2.1 Recommended ISO5500 Application Circuit

The ISO5500 has both, inverting and non-inverting gate control inputs, an active low reset input, and an open drain fault output suitable for wired-OR applications. The recommended application circuit in Figure 62 illustrates a typical gate drive implementation using the ISO5500.

The four 0.1 μF supply bypass capacitors provide the large transient currents necessary during a switching transition. Because of the transient nature of the charging currents, low current (20 mA) power supplies for V_{CC2} and V_{EE-P} suffice. The 100 pF blanking capacitor disables DESAT detection during the off-to-on transition of the power device. The DESAT diode and its 100 Ω series resistor are important external protection components for the fault detection circuitry. The 10 Ω gate resistor limits the gate charge current and indirectly controls the IGBT collector voltage rise and fall times. The open-drain fault output has a passive 3.3 k Ω pull-up resistor and a 330 pF filtering capacitor. In this application, the IGBT gate driver will shut down when a fault is detected and will not resume switching until the micro-controller applies a reset signal.

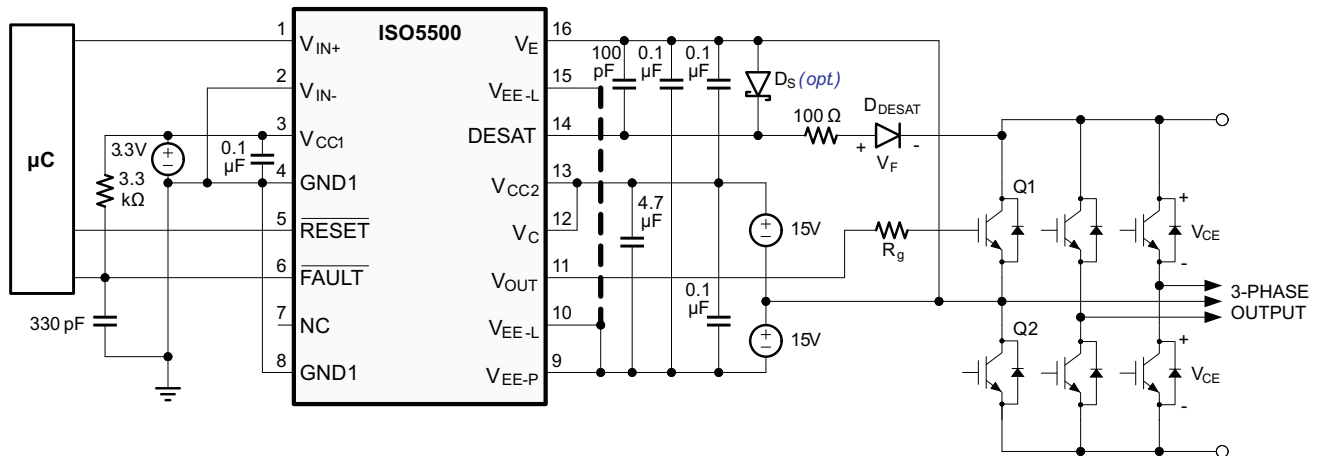


Figure 62. Recommended Application Circuit

9.2.2.2 $\overline{\text{FAULT}}$ Pin Circuitry

The $\overline{\text{FAULT}}$ pin is an open-drain output requiring a 3.3 k Ω pull-up resistor to provide logic high when $\overline{\text{FAULT}}$ is inactive.

Because fast common mode transients can alter the $\overline{\text{FAULT}}$ -pin voltage during high state, a 330 pF capacitor connected between $\overline{\text{FAULT}}$ and GND1 is recommended to provide sufficient noise margin at the specified CMTI of 50 kV/ μs . The added capacitance does not increase the $\overline{\text{FAULT}}$ response time during a fault condition.

Typical Application (continued)

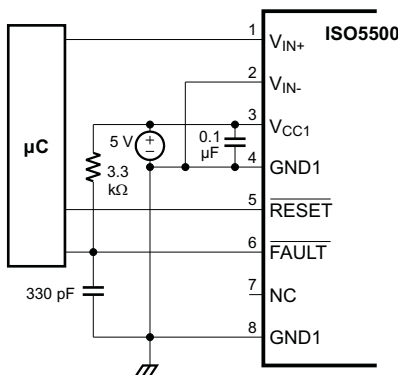


Figure 63. FAULT Pin Circuitry for High CMTI

9.2.2.3 Driving the Control Inputs

The amount of common-mode transient immunity (CMTI) is primarily determined by the capacitive coupling from the high-voltage output circuit to the low-voltage input side of the ISO5500. For maximum CMTI performance, the digital control inputs, V_{IN+} and V_{IN-} , must be actively driven by standard CMOS or TTL, push-pull drive circuits. This type of low-impedance signal source provides active drive signals that prevent unwanted switching of the ISO5500 output under extreme common-mode transient conditions. Passive drive circuits, such as open-drain configurations using pull-up resistors, must be avoided.

9.2.2.4 Local Shutdown and Reset

In applications with local shutdown and reset, the $\overline{\text{FAULT}}$ output of each gate driver is polled separately, and the individual reset lines are asserted low independently to reset the motor controller after a fault condition.

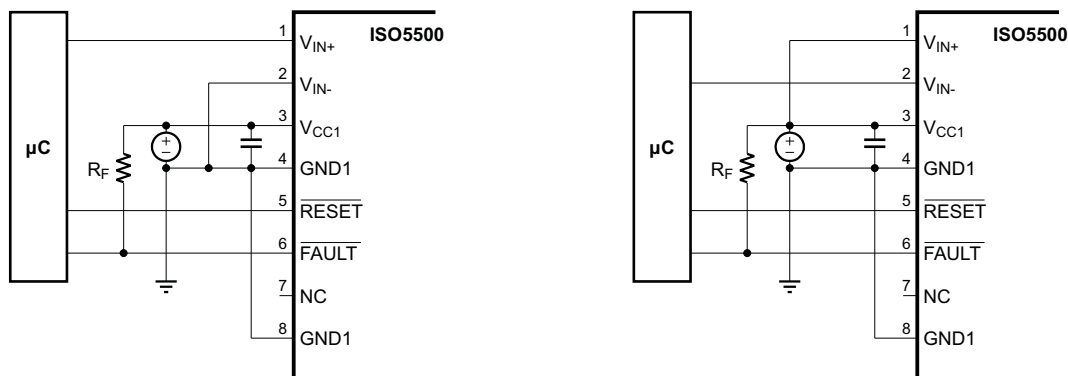


Figure 64. Local Shutdown and Reset for Noninverting (left) and Inverting Input Configuration (right)

9.2.2.5 Global Shutdown and Reset

When configured for inverting operation, the ISO5500 can be configured to shutdown automatically in the event of a fault condition by tying the $\overline{\text{FAULT}}$ output to V_{IN+} . For high reliability drives, the open drain $\overline{\text{FAULT}}$ outputs of multiple ISO5500 devices can be wired together forming a single, common fault bus for interfacing directly to the microcontroller. When any of the six gate drivers of a three-phase inverter detects a fault, the active low $\overline{\text{FAULT}}$ output disables all six gate drivers simultaneously; thereby, providing protection against further catastrophic failures.

Typical Application (continued)

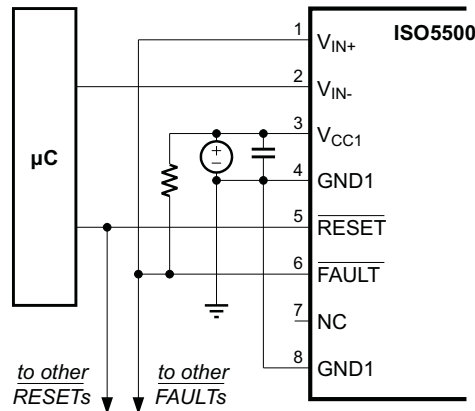


Figure 65. Global Shutdown with Inverting Input Configuration

9.2.2.6 Auto-Reset

Connecting $\overline{\text{RESET}}$ to the active control input ($V_{\text{IN}+}$ for non-inverting, or $V_{\text{IN}-}$ for inverting operation) configures the ISO5500 for automatic reset capability. In this case, the gate control signal at V_{IN} is also applied to the $\overline{\text{RESET}}$ input to reset the fault latch every switching cycle. During normal IGBT operation, asserting $\overline{\text{RESET}}$ low has no effect on the output. For a fault condition, however, the gate driver remains in the latched fault state until the gate control signal changes to the 'gate low' state and resets the fault latch.

If the gate control signal is a continuous PWM signal, the fault latch will always be reset before $V_{\text{IN}+}$ goes high again. This configuration protects the IGBT on a cycle by cycle basis and automatically resets before the next 'on' cycle. When the ISO5500 is configured for Auto Reset, the specified minimum $\overline{\text{FAULT}}$ signal pulse width is 3 μs .

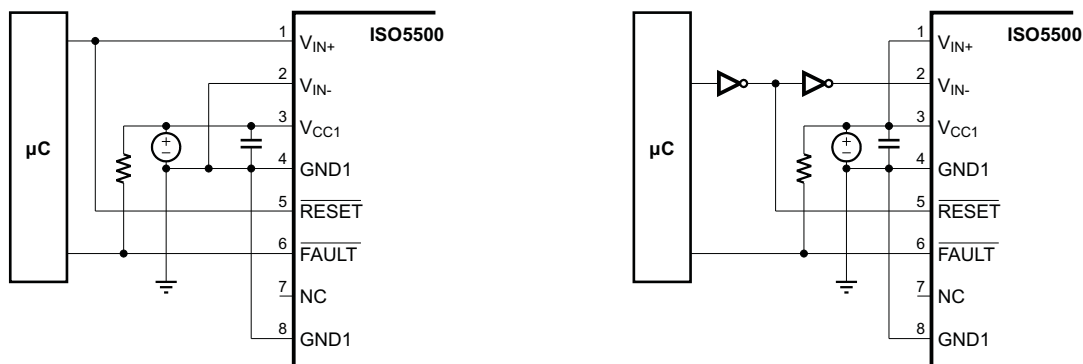


Figure 66. Auto Reset for Non-inverting and Inverting Input Configuration

9.2.2.7 Resetting Following a Fault Condition

To resume normal switching operation following a fault condition ($\overline{\text{FAULT}}$ output low), the gate control signal must be driven into a 'gate low' state before asserting $\overline{\text{RESET}}$ low. This can be accomplished with a microcontroller, or an additional logic gate that synchronizes the $\overline{\text{RESET}}$ signal with the appropriate input signal.

Typical Application (continued)

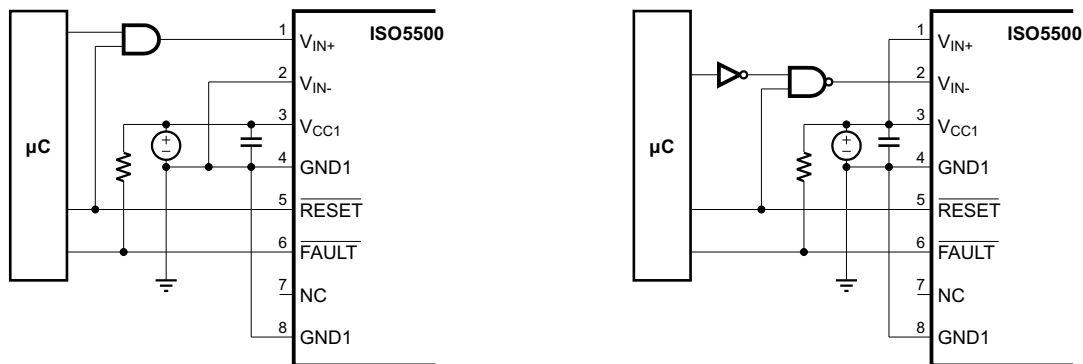


Figure 67. Auto Reset with Prior Gate-low Assertion for Non-inverting and Inverting Input Configuration

9.2.2.8 DESAT Pin Protection

Switching inductive loads causes large instantaneous forward voltage transients across the freewheeling diodes of IGBTs. These transients result in large negative voltage spikes on the DESAT pin which draw substantial current out of the device. To limit this current below damaging levels, a 100 Ω to 1 k Ω resistor is connected in series with the DESAT diode. The added resistance neither alters the DESAT threshold nor the DESAT blanking time.

Further protection is possible through an optional Schottky diode, whose low forward voltage assures clamping of the DESAT input to V_F potential at low voltage levels.

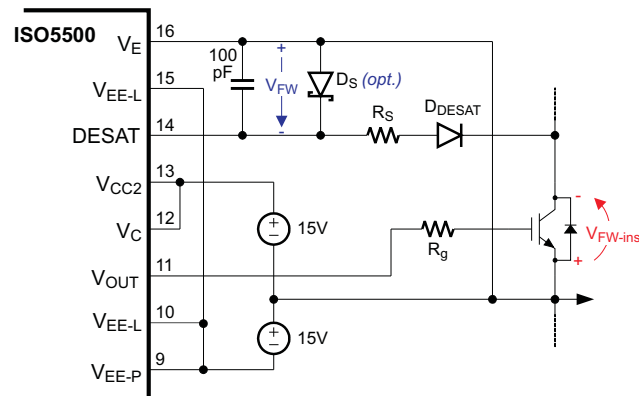


Figure 68. DESAT Pin Protection with Series Resistor and Optional Schottky Diode

9.2.2.9 DESAT Diode and DESAT Threshold

The DESAT diode's function is to conduct forward current, allowing sensing of the IGBT's saturated collector-to-emitter voltage, V_{CESAT} , (when the IGBT is "on") and to block high voltages (when the IGBT is "off"). During the short transition time when the IGBT is switching, there is commonly a high dV_{CE}/dt voltage ramp rate across the IGBT. This results in a charging current $I_{CHARGE} = C_{D-DESAT} \times dV_{CE}/dt$, charging the blanking capacitor.

To minimize this current and avoid false DESAT triggering, fast switching diodes with low capacitance are recommended. As the diode capacitance builds a voltage divider with the blanking capacitor, large collector voltage transients appear at DESAT attenuated by the ratio of $1 + C_{\text{BLANK}} / C_{\text{D-DESAT}}$.

Table 3 lists a number of fast-recovery diodes suitable for the use as DESAT diodes.

Because the sum of the DESAT diode forward-voltage and the IGBT collector-emitter voltage make up the voltage at the DESAT-pin, $V_F + V_{CE} = V_{DESAT}$, the V_{CE} level, which triggers a fault condition, can be modified by adding multiple DESAT diodes in series: $V_{CE-FAULT(TH)} = 7.2 \text{ V} - n \times V_F$ (where n is the number of DESAT diodes).

Typical Application (continued)

When using two diodes instead of one, diodes with half the required maximum reverse-voltage rating may be chosen.

Table 3. Recommended DESAT Diodes

PART NUMBER	MANUFACTURER	t _{rr} (ns)	V _{RRM-max} (V)	PACKAGE
STTH112	STM	75	1200	SMA, SMB, DO-41
MUR100E	Motorola	75	1000	59-04 (axial leaded)
MURS160T3	Motorola	75	600	Case 403A (SMD)
UF4007	General Semi.	75	1000	DO-204AL (axial leaded)
BYM26E	Philips	75	1000	SOD64 (axial leaded)
BYV26E	Philips	75	1000	SOD57 (axial leaded)
BYV99	Philips	75	600	SOD87 (axial leaded)

9.2.2.10 Determining the Maximum Available, Dynamic Output Power, P_{OD-max}

The ISO5500 total power consumption of P_D = 592 mW consists of the total input power, P_{ID}, the total output power, P_{OD}, and the output power under load, P_{OL}:

$$P_D = P_{ID} + P_{OD} + P_{OL} \quad (2)$$

With:

$$P_{ID} = V_{CC1-max} \times I_{CC1-max} = 5.5 \text{ V} \times 8.5 \text{ mA} = 47 \text{ mW} \quad (3)$$

and:

$$P_{OD} = (V_{CC2} - V_{EE-P}) \times I_{CC2-q} = 30 \text{ V} \times 14 \text{ mA} = 420 \text{ mW} \quad (4)$$

then:

$$P_{OL} = P_D - P_{ID} - P_{OD} = 592 \text{ mW} - 47 \text{ mW} - 420 \text{ mW} = 125 \text{ mW} \quad (5)$$

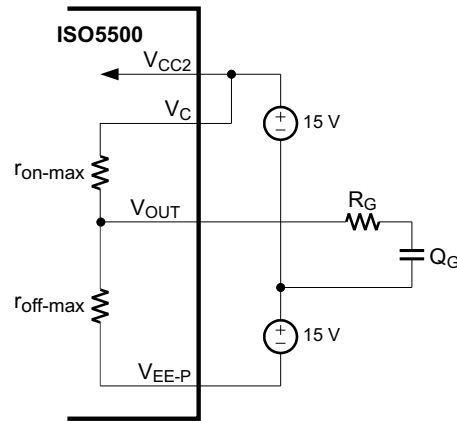
In comparison to P_{OL}, the actual dynamic output power under worst case condition, P_{OL-WC}, depends on a variety of parameters:

$$P_{OL-WC} = 0.5 \times f_{INP} \times Q_G \times (V_{CC2} - V_{EE-P}) \times \left(\frac{r_{on-max}}{r_{on-max} + R_G} + \frac{r_{off-max}}{r_{off-max} + R_G} \right)$$

where

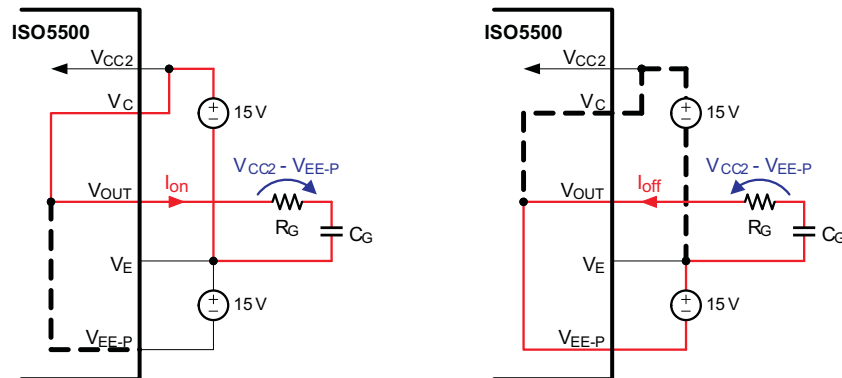
- f_{INP} = signal frequency at the control input V_{IN(±)}
 - Q_G = power device gate charge
 - V_{CC2} = positive output supply with respect to V_E
 - V_{EE-P} = negative output supply with respect to V_E
 - r_{on-max} = worst case output resistance in the on-state: 4Ω
 - r_{off-max} = worst case output resistance in the off-state: 2.5Ω
 - R_G = gate resistor
- (6)

Once R_G is determined, Equation 6 is to be used to verify whether P_{OL-WC} < P_{OL}. Figure 69 shows a simplified output stage model for calculating P_{OL-WC}.


Figure 69. Simplified Output Model for Calculating P_{OL-wc}

9.2.2.11 Determining Gate Resistor, R_G

The value of the gate resistor determines the peak charge and discharge currents, I_{ON-PK} and I_{OFF-PK} . Due to the transient nature of these currents, their peak values only occur during the on-to-off and off-to-on transitions of the gate voltage. In order to calculate R_G for the maximum peak current, r_{on} and r_{off} must be assumed zero. The resulting charge and discharge models are shown in Figure 70.


Figure 70. Simplified Gate Charge and Discharge Model

9.2.2.11.1 Off-to-On Transition

In the off-state, the upper plate of the gate capacitance, C_G , assumes a steady-state potential of $-V_{EE-P}$ with respect to V_E . When turning on the power device, V_{CC2} is applied to V_{OUT} and the voltage drop across R_G results in a peak charge current of $I_{ON-PK} = (V_{CC2} - V_{EE-P})/R_G$. Solving for R_G then provides the necessary resistor value for a desired on-current via:

$$R_G = \frac{V_{CC2} - V_{EE-P}}{I_{ON-PK}} \quad (7)$$

9.2.2.11.2 On-to-Off Transition

When turning the power device off, the current and voltage relations are reversed but the equation for calculating R_G remains the same.

Once R_G has been calculated, it is necessary to check whether the resulting, worst-case power consumption, P_{OD-WC} , (derived in Equation 6) is below the calculated maximum, $P_{OL} = 125 \text{ mW}$ (calculated in Equation 5).

9.2.2.12 Example

The example below considers an IGBT drive with the following parameters:

$$I_{ON-PK} = 2 \text{ A}, Q_G = 650 \text{ nC}, f_{INP} = 20 \text{ kHz}, V_{CC2} = 15 \text{ V}, V_{EE-P} = -5 \text{ V}$$

Applying Equation 7, the value of the gate resistor is calculated with

$$R_G = \frac{15 \text{ V} - (-5 \text{ V})}{2 \text{ A}} = 10 \Omega \quad (8)$$

Then, calculating the worst-case output power consumption as a function of R_G , using Equation 6 yields

$$P_{OL-WC} = 0.5 \times 20 \text{ kHz} \times 650 \text{ nC} \times (15 \text{ V} - (-5 \text{ V})) \times \left(\frac{4 \Omega}{4 \Omega + 10 \Omega} + \frac{2.5 \Omega}{2.5 \Omega + 10 \Omega} \right) = 63 \text{ mW} \quad (9)$$

Because $P_{OL-WC} = 63 \text{ mW}$ is well below the calculated maximum of $P_{OL} = 125 \text{ mW}$, the resistor value of $R_G = 10 \Omega$ is fully suitable for this application.

9.2.2.13 Determining Collector Resistor, R_C

Despite equal charge and discharge currents, many power devices possess longer turn-off propagation and fall times than turn-on propagation and rise times. In order to compensate for the difference in switching times, it might be necessary to significantly reduce the charge current, I_{ON-PK} , versus the discharge current, I_{OFF-PK} .

Reducing I_{ON-PK} is accomplished by inserting an external resistor, R_C , between the V_C - pin and the V_{CC2} - pin of the ISO5500.

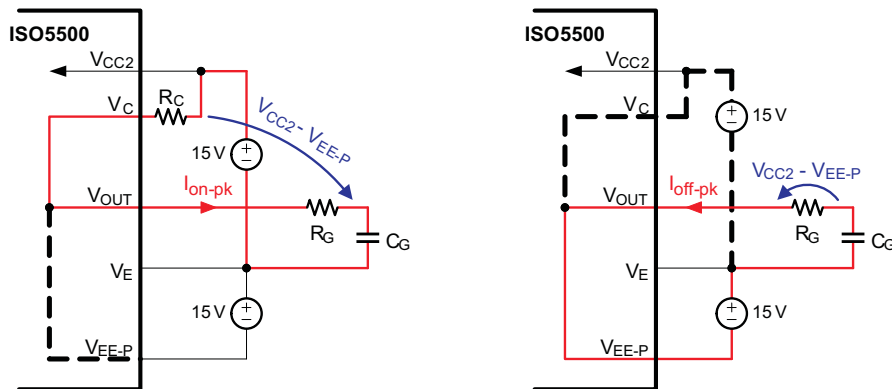


Figure 71. Reducing I_{ON-PK} by Inserting Resistor R_C

Figure 71 (right) shows that during the on-transition, the $(V_{CC2} - V_{EE-P})$ voltage drop occurs across the series resistance of $R_C + R_G$, thus reducing the peak charge current to: $I_{ON-PK} = (V_{CC2} - V_{EE-P}) / (R_C + R_G)$. Solving for R_C provides:

$$R_C = \frac{V_{CC2} - V_{EE-P}}{I_{ON-PK}} - R_G \quad (10)$$

To stay below the maximum output power consumption, R_G must be calculated first via:

$$R_G = \left| \frac{V_{CC2} - V_{EE-P}}{I_{OFF-PK}} \right| \quad (11)$$

and the necessary comparison of P_{OL-WC} versus P_{OL} must be completed.

Once R_G is determined, calculate R_C for a desired on-current using Equation 10.

Another method is to insert Equation 11 into Equation 10 and arriving at:

$$R_C = R_G \times \left(\frac{I_{OFF-PK}}{I_{ON-PK}} - 1 \right) \quad (12)$$

9.2.2.13.1 Example

Reducing the peak charge current from the previous example to $I_{ON-PK} = 1.5 \text{ A}$, requires a R_C value of:

$$R_C = 10 \, \Omega \times \left(\frac{2 \text{ A}}{1.5 \text{ A}} - 1 \right) = 3.33 \, \Omega \quad (13)$$

9.2.2.14 Higher Output Current Using an External Current Buffer

To increase the IGBT gate drive current, a non-inverting current buffer (such as the npn/pnp buffer shown in Figure 72) may be used. Inverting types are not compatible with the desaturation fault protection circuitry and must be avoided. The MJD44H11/MJD45H11 pair is appropriate for currents up to 8 A, the D44VH10/ D45VH10 pair for up to 15 A maximum.

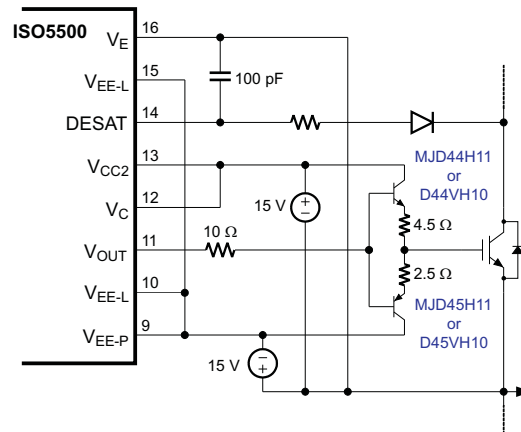


Figure 72. Current Buffer for Increased Drive Current

9.2.3 Application Curve

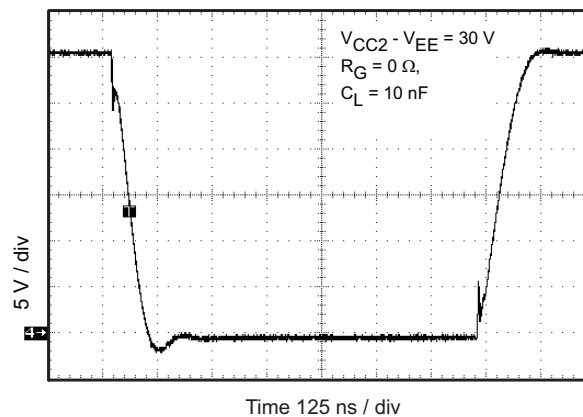


Figure 73. Output Waveform

10 Power Supply Recommendations

To provide the large transient currents necessary during a switching transition on the gate driver output, 0.1- μ F bypass capacitors are recommended between input supply and ground (V_{CC1} and GND1), and between output supplies and ground (V_{CC2} and V_E , V_{CC2} and V_{EE-P} and V_{EE-P} and V_E). These capacitors are shown in [Figure 62](#). These capacitors should be placed as close to the supply and ground pins as possible.

11 Layout

11.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see [Figure 74](#)). Layer stacking should be in the following order (top-to-bottom): high-current or sensitive signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-current or sensitive traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the gate driver and the microcontroller and power transistors. Gate driver control input, Gate driver output V_{OUT} and DESAT should be routed in the top layer.
- Placing a solid ground plane next to the sensitive signal layer provides an excellent low-inductance path for the return current flow. On the driver side, use V_E as the ground plane.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/in². On the gate-driver V_{EE-P} and V_{CC2} can be used as power planes. They can share the same layer on the PCB as long as they are not connected together.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

For more detailed layout recommendations, including placement of capacitors, impact of vias, reference planes, routing etc. see Application Note [SLLA284](#), *Digital Isolator Design Guide*.

11.2 PCB Material

Standard FR-4 epoxy-glass is recommended as PCB material. FR-4 (Flame Retardant 4) meets the requirements of Underwriters Laboratories UL94-V0, and is preferred over cheaper alternatives due to its lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and its self-extinguishing flammability-characteristics.

11.3 Layout Example

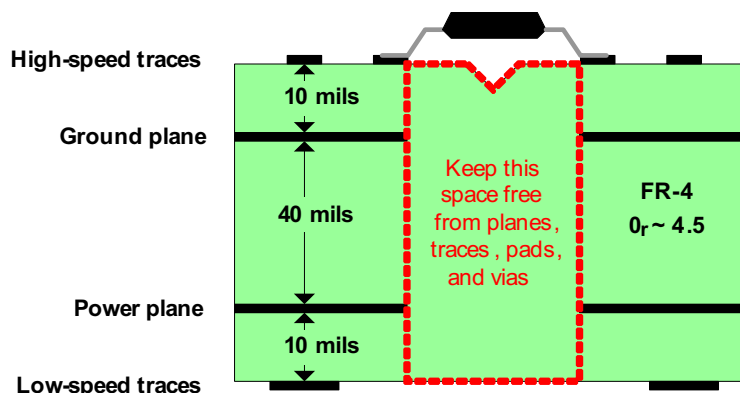


Figure 74. Recommended Layer Stack

12 器件和文档支持

12.1 器件支持

12.1.1 第三方产品免责声明

TI 发布的与第三方产品或服务有关的信息，不能构成与此类产品或服务或保修的适用性有关的认可，不能构成此类产品或服务单独或与任何 TI 产品或服务一起的表示或认可。

12.2 文档支持

12.2.1 相关文档

相关文档如下：

- 《ISO5500 评估模块 (EVM) 用户指南》，[SLLU136](#)
- 《数字隔离器设计指南》，[SLLA284](#)

12.2.1.1 术语表

[SLYZ022](#) — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

12.3 商标

All trademarks are the property of their respective owners.

12.4 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

[SLLA353](#) -- 《隔离相关术语》。

13 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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数字音频	www.ti.com.cn/audio	通信与电信	www.ti.com.cn/telecom
放大器和线性器件	www.ti.com.cn/amplifiers	计算机及周边	www.ti.com.cn/computer
数据转换器	www.ti.com.cn/dataconverters	消费电子	www.ti.com.cn/consumer-apps
DLP® 产品	www.dlp.com	能源	www.ti.com.cn/energy
DSP - 数字信号处理器	www.ti.com.cn/dsp	工业应用	www.ti.com.cn/industrial
时钟和计时器	www.ti.com.cn/clockandtimers	医疗电子	www.ti.com.cn/medical
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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISO5500DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	ISO5500DW	Samples
ISO5500DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	ISO5500DW	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

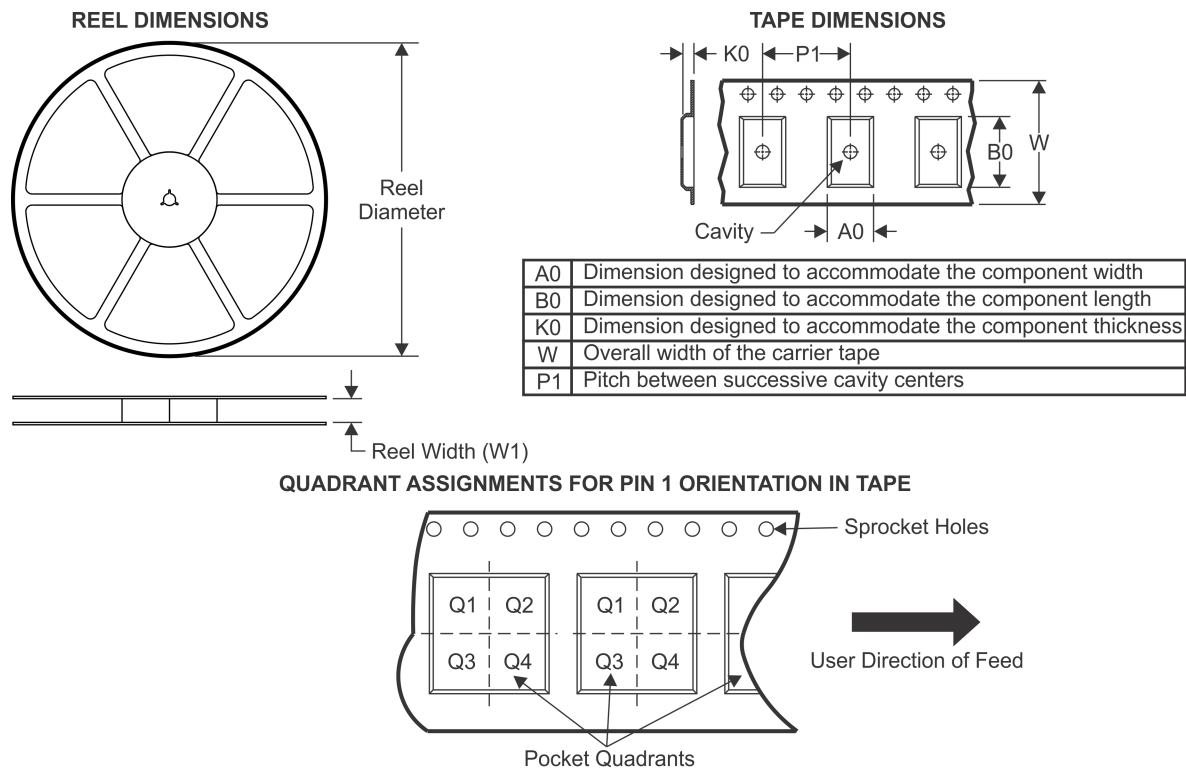
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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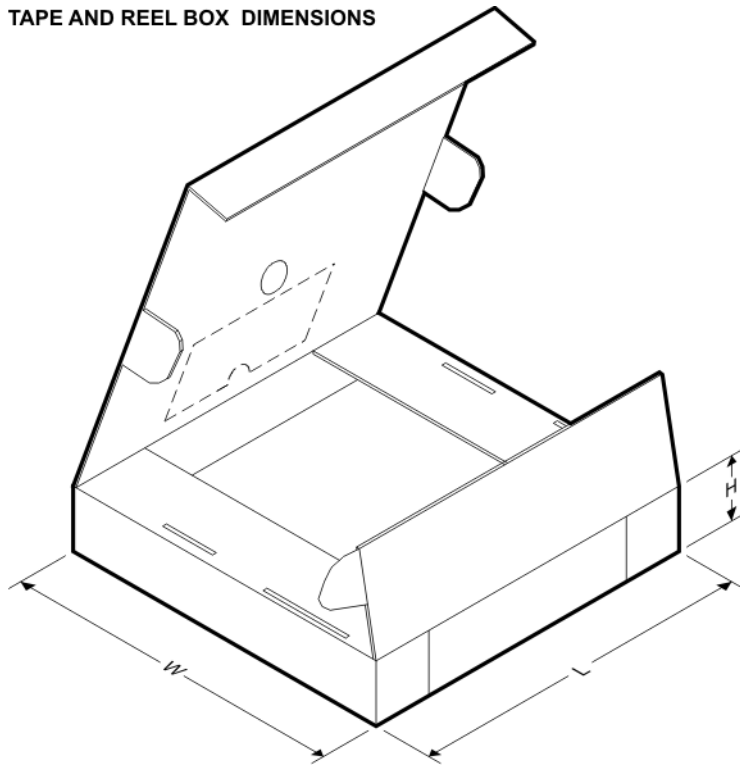
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TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO5500DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO5500DWR	SOIC	DW	16	2000	350.0	350.0	43.0

GENERIC PACKAGE VIEW

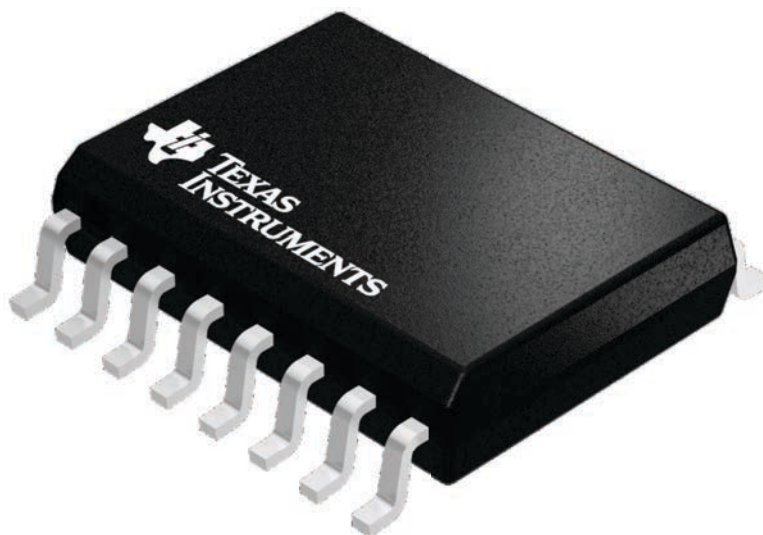
DW 16

SOIC - 2.65 mm max height

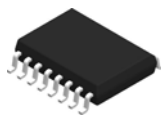
7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4224780/A

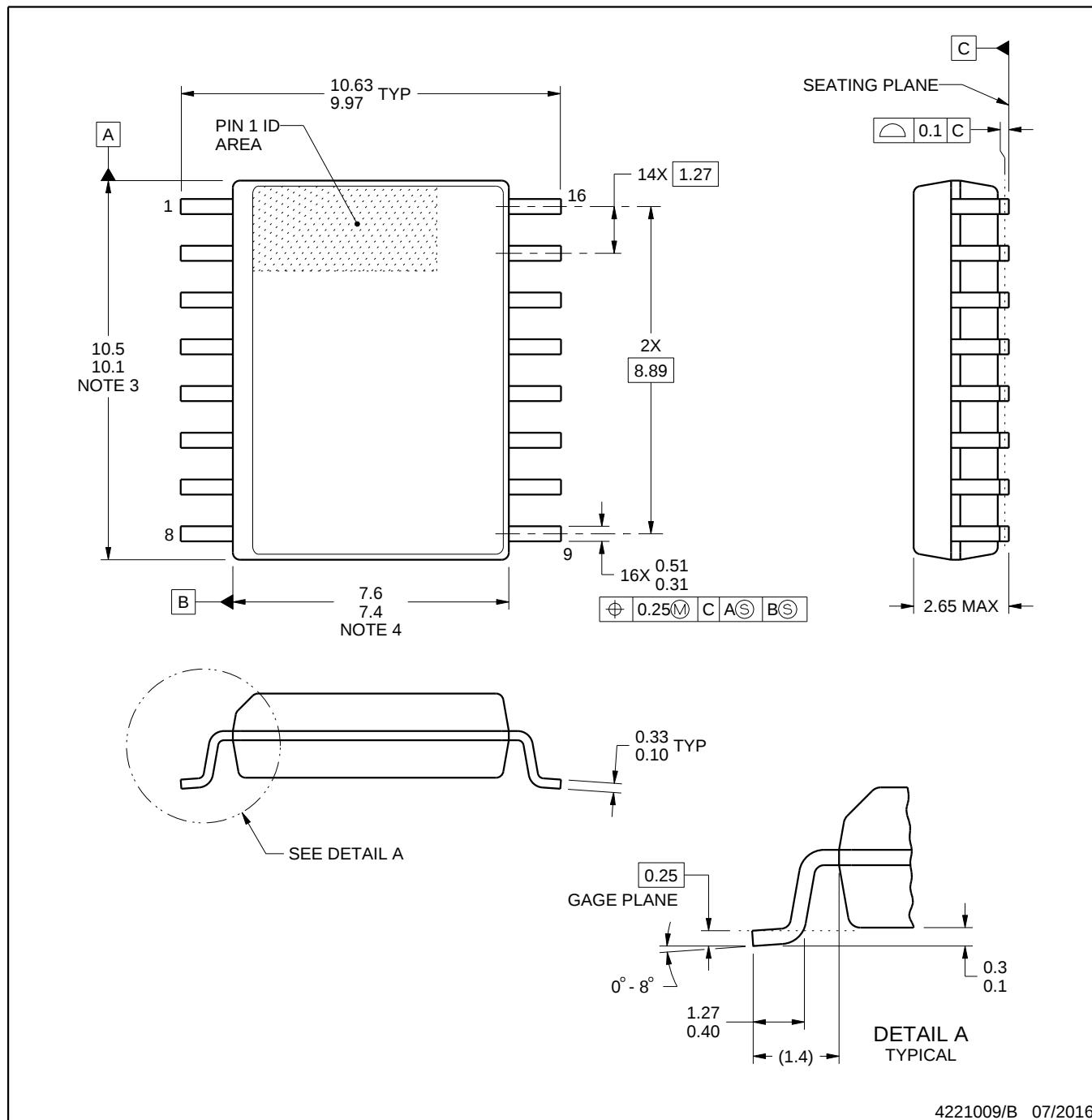


DW0016B

PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



4221009/B 07/2016

NOTES:

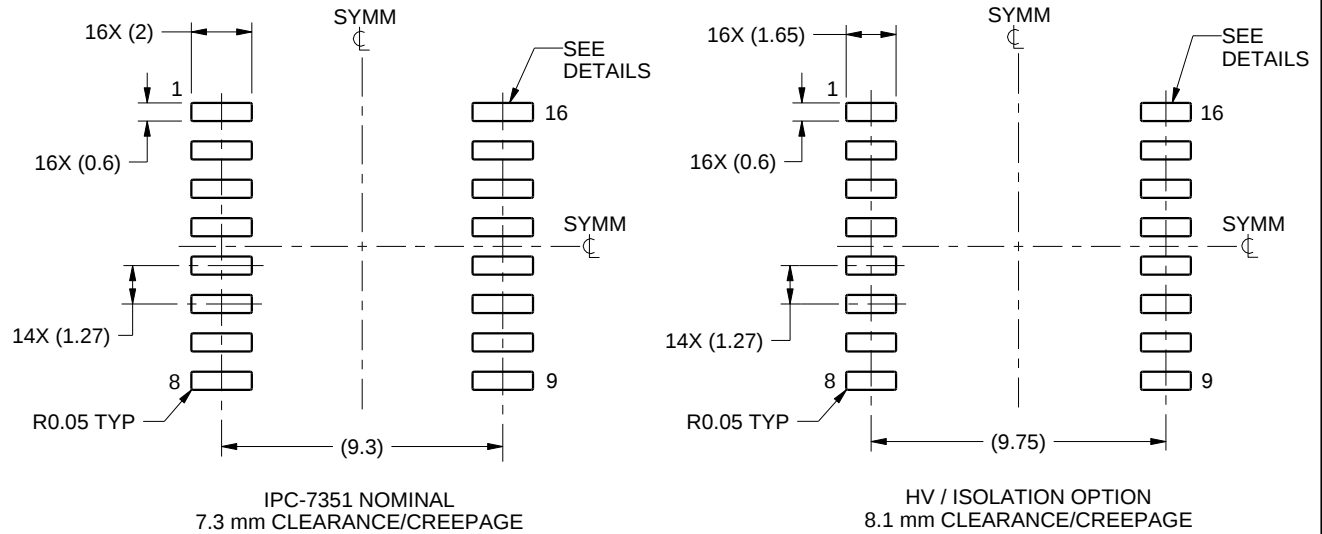
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

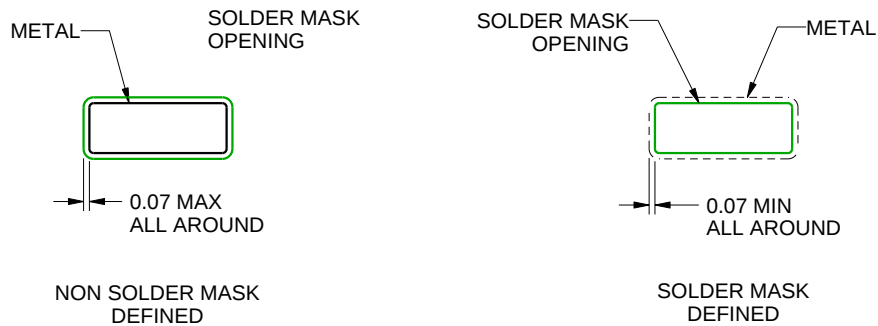
DW0016B

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:4X



SOLDER MASK DETAILS

4221009/B 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

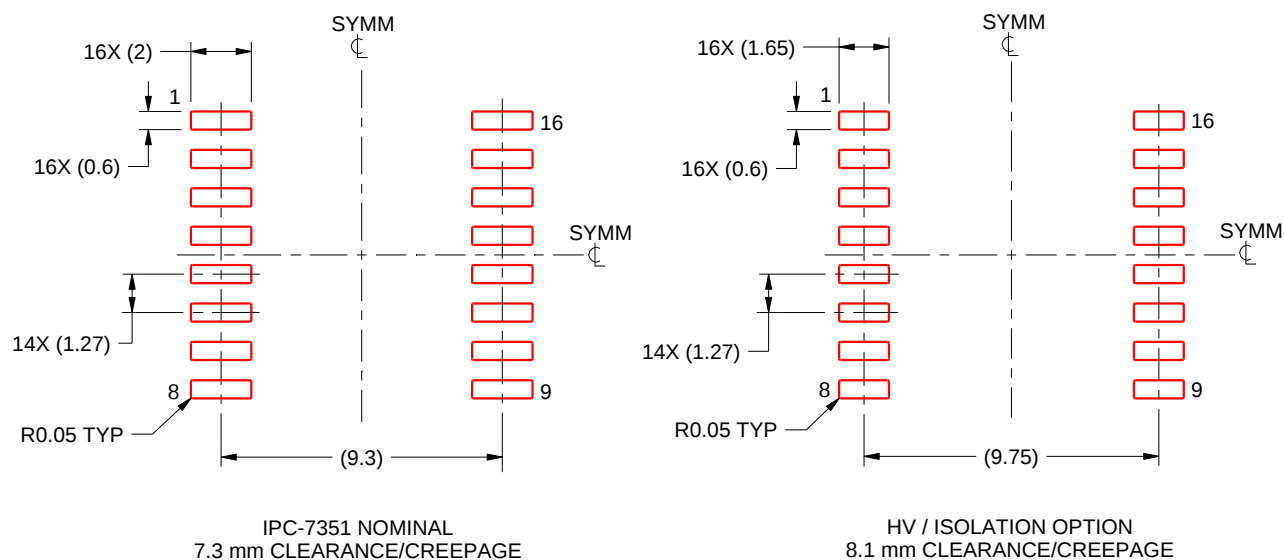
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0016B

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:4X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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